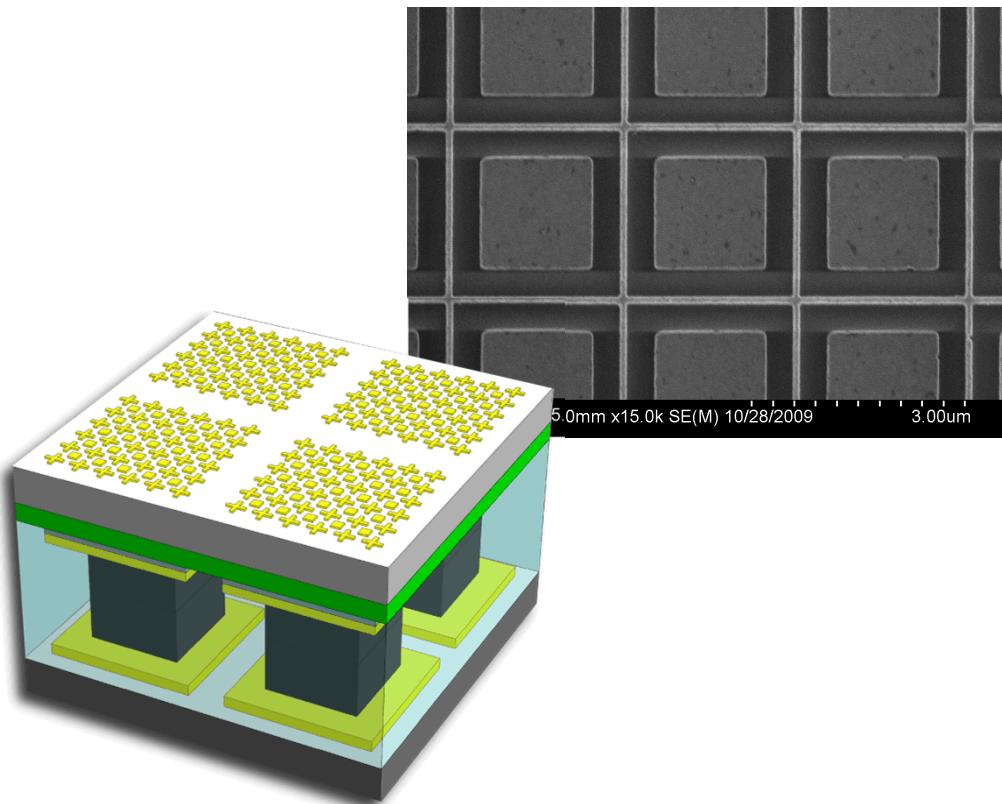


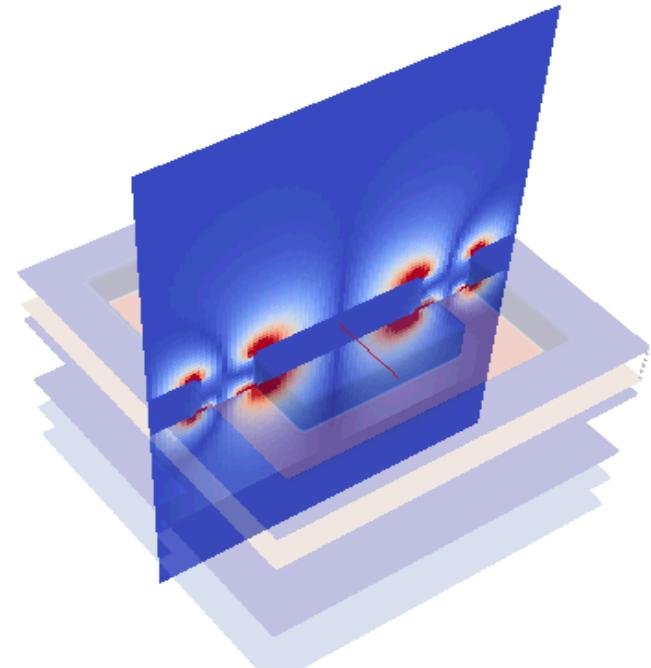
*Exceptional service in the national interest*



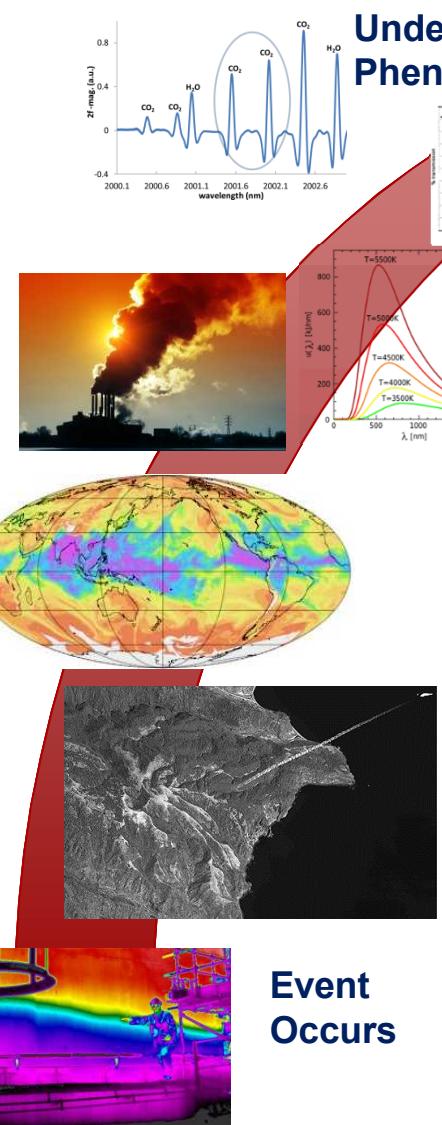
# Field confinement using metasurfaces for increased-efficiency III-V infrared detectors



Jin Kim and David Peters  
Sandia National Laboratories

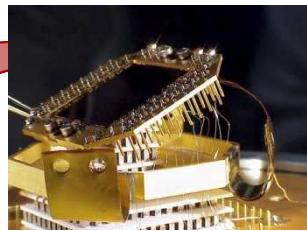


# The Steps of Sensing

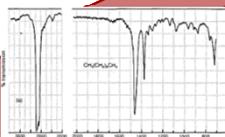
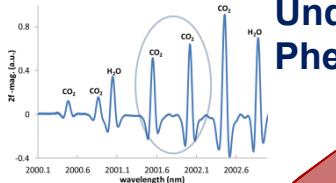


Event  
Occurs

## Sense It

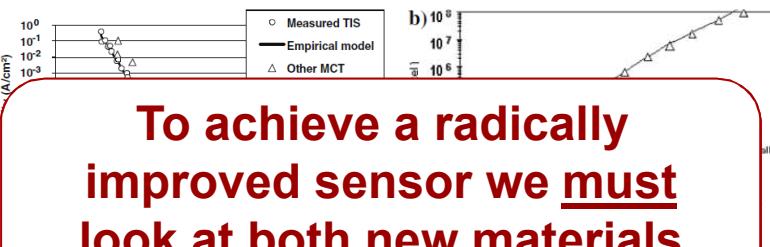


Understand  
Phenomenology



### Limits in current technology

- Cut-off wavelength determined at manufacture
- Noise is nearing its floor for this architecture



To achieve a radically improved sensor we must look at both new materials and architectures.

Changes in material composition or architecture tweaks are not going to lead to radical improvement.

## Control, Pre-process and Transmit the Data



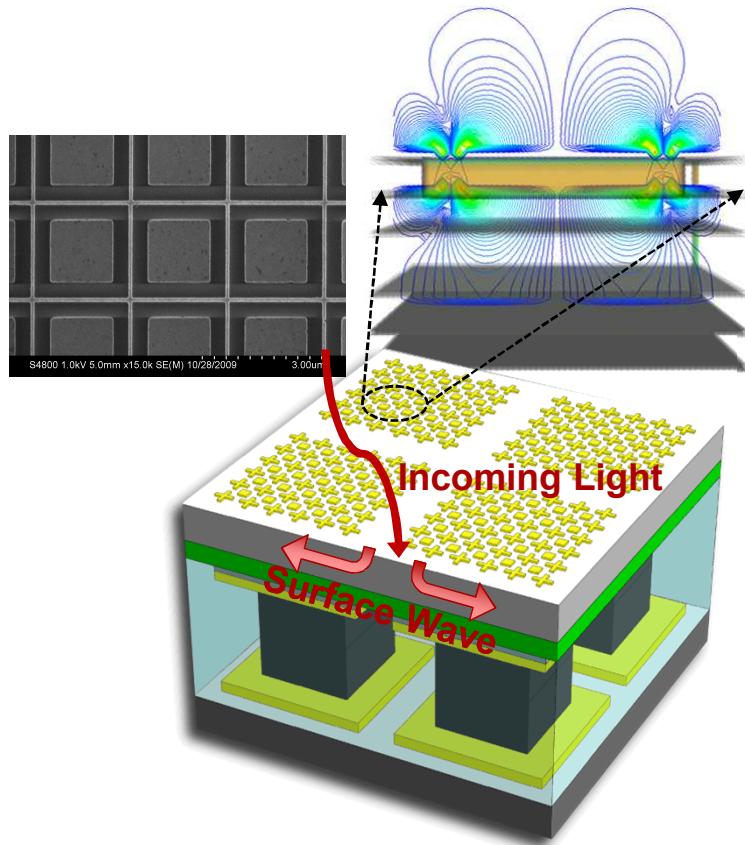
## Understand the Data

## Take Action



# The Enabling Technology: Nanoantennas

## What is a nanoantenna?



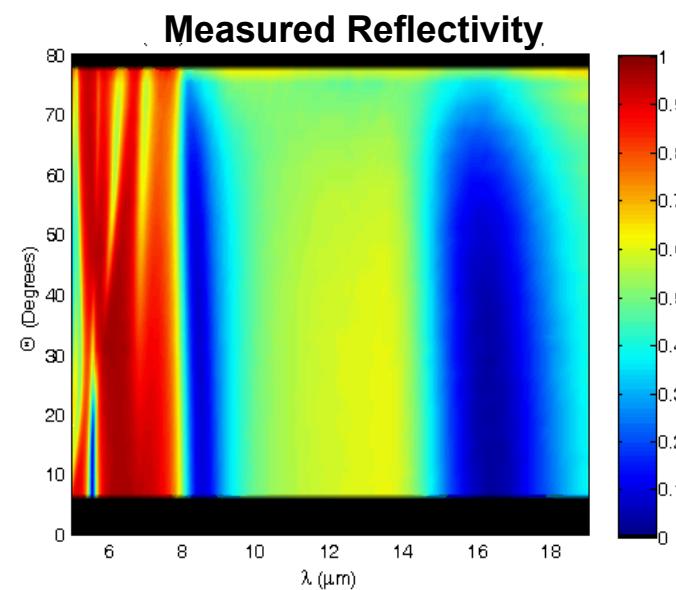
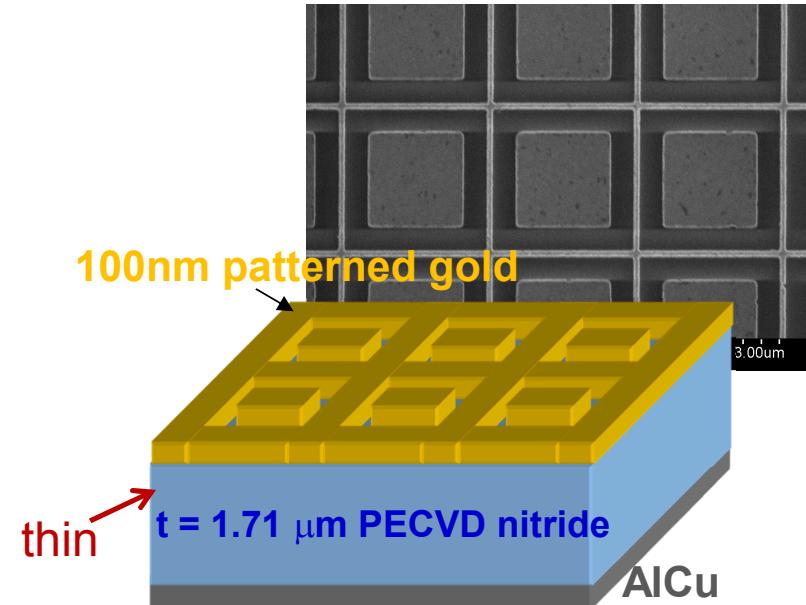
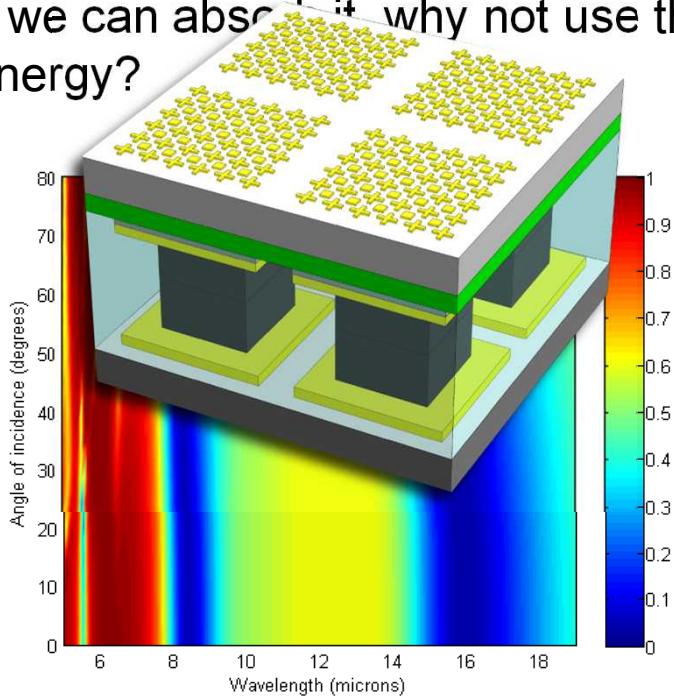
- A subwavelength patterning of metal or high-index dielectric
- The nanoantenna converts incoming radiation to a surface wave with energy confined to a small volume
- The pattern may be changed from pixel-to-pixel allowing adjacent pixels to have different spectral or polarization response
- Built-in A/R “coating”
- Angular insensitivity

# Outline

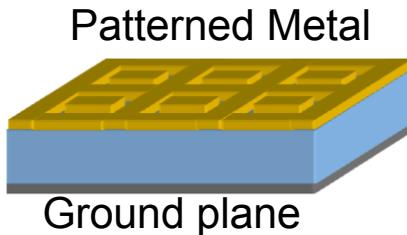
- Background
  - Perfect absorbers
  - Field confinement
- nBn Material
  - Material choices
  - Changes that thin absorber layer allows
- Nanoantenna Development
  - Finite size of pixels
  - Where absorption occurs
- Integration Challenges

# Background: Perfect Absorbers

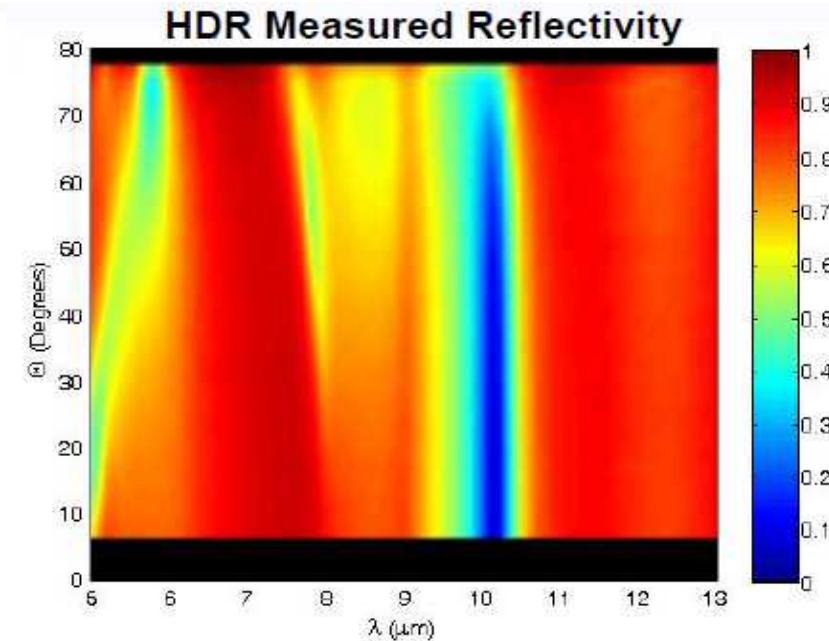
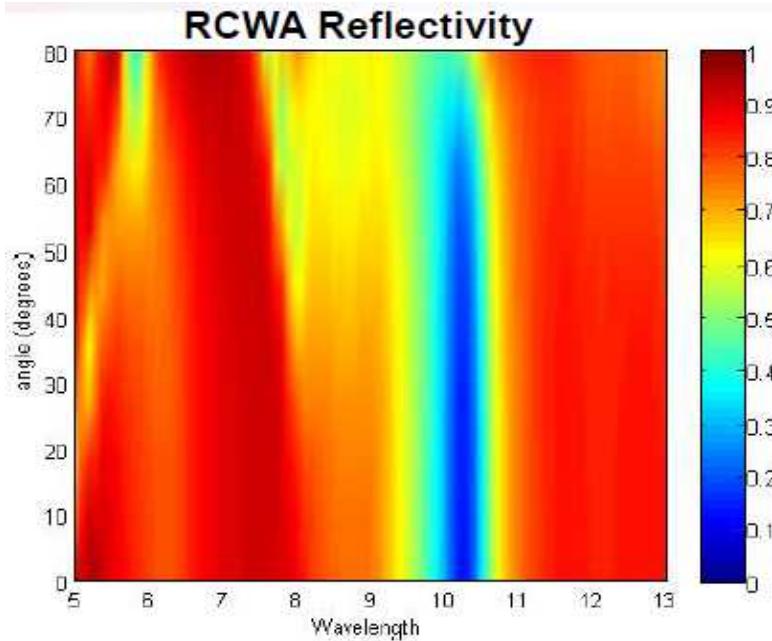
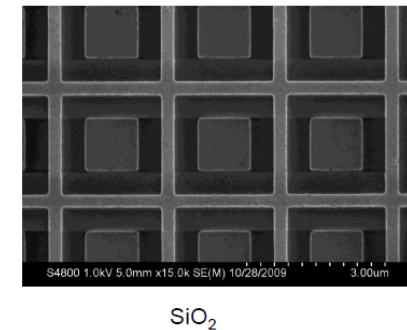
- We designed and made a dual-band perfect absorber.
- Excellent agreement between simulation and measurement. → Great confidence in our models.
- Measured absorption of 99% in two bands.
- A resonant structure.
- If we can absorb it, why not use that energy?



# Early Perfect Absorber Work: SiO<sub>2</sub>



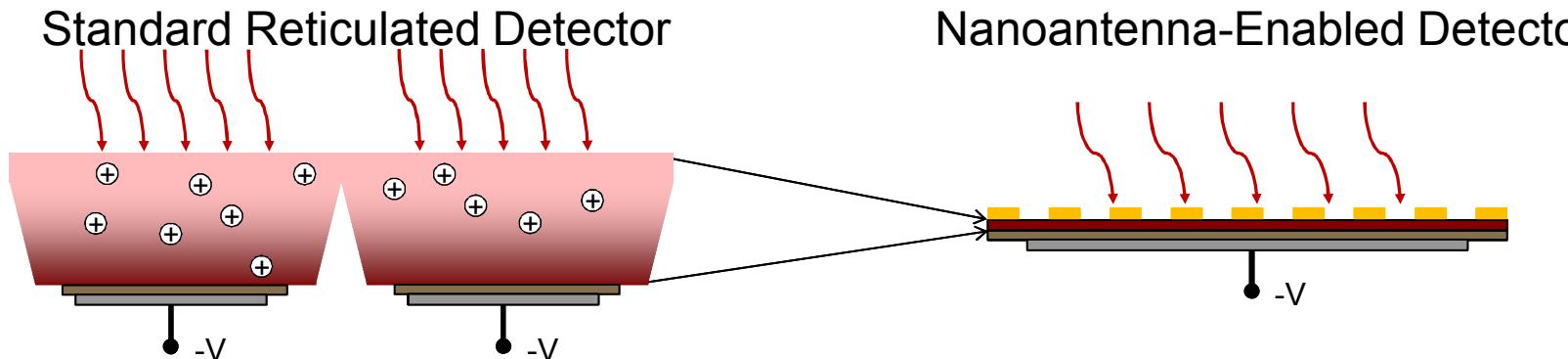
These type nanoantennas consisting of a patterned metal layer semiconductor/dielectric metal backplane are inherently angle insensitive.



D. W. Peters, G. R. Hadley, A. A. Cruz-Cabrera, L. I. Basilio, J. R. Wendt, S. A. Kemme, T. R. Carter, S. Samora, "Infrared Frequency Selective Surfaces for sensor applications," Proc. of SPIE, vol. 7298, 7298 3L, Apr. 2009.

D.W. Peters, P. Davids, J.R. Wendt, A.A. Cruz-Cabrera, S.A. Kemme, S. Samora, "Metamaterial-inspired high-absorption surfaces for thermal infrared applications," Proc. of SPIE, vol. 7609, 2010.

# Using Confinement for Improving Detectors



## Dark Current

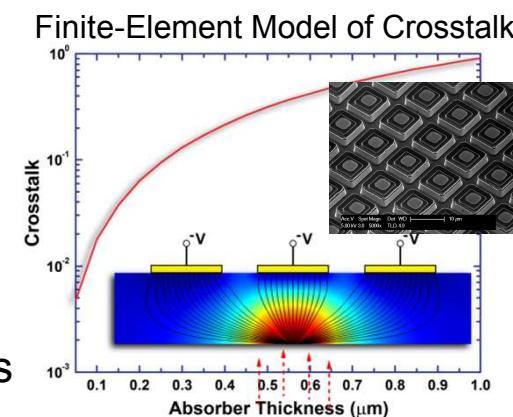
- Leads to noise.
- Is reduced by cooling the detector.
- Is proportional to the volume of active material.

$$Dark\ Current\ J_{Diff} = \frac{e \cdot n_i^2 \cdot t_{abs}}{N_D \cdot \tau_p}$$

**Less volume of active material leads to less dark current.**

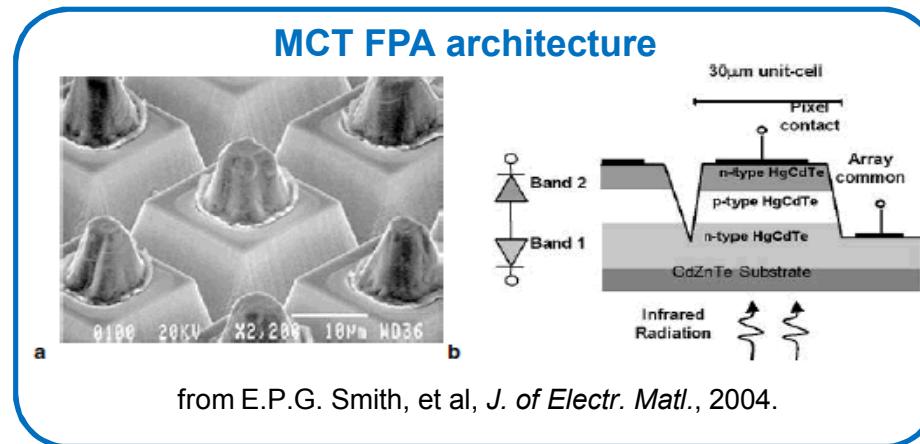
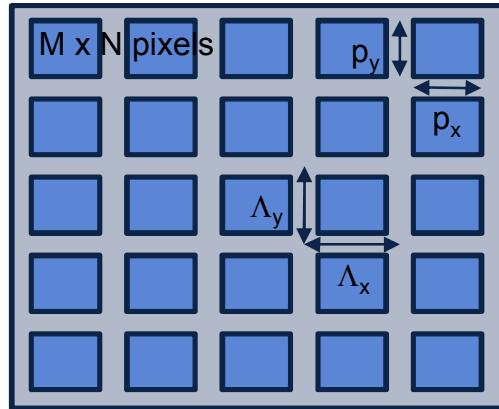
## Crosstalk

- Causes image blur and loss of resolution.
- Reticulated detectors suffer reduced fill factors.
- Etched sidewalls lead to increased surface recombination/generation.
- Exponential reduction in crosstalk with reduced absorber thickness.
- No loss of fill factor or creation of surface states with nanoantenna detector design.

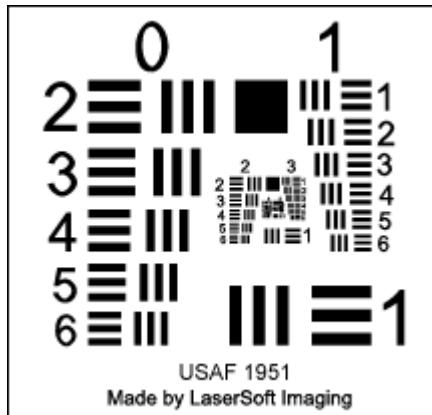


**In the IR, the limitation to further reducing pixel size is crosstalk.**

# Maximizing Active Area Improves MTF and Signal



$$\text{MTF}(f_x, f_y) = [\text{sinc}((M \cdot \Lambda_x) \cdot f_x, (N \cdot \Lambda_y) \cdot \eta) * \text{comb}(\Lambda_x \cdot f_x, \Lambda_y \cdot f_y)] \cdot \text{sinc}(p_x \cdot f_x, p_y \cdot f_y)$$



- Ideally for the MTF function, we want  $\Lambda_x$ ,  $\Lambda_y$  as small as possible to maximize the MTF (small pixels = better MTF).
- This is clearly impossible, but we can make  $\Lambda_x$  and  $\Lambda_y$  as small as possible for a given  $p_x$  and  $p_y$  (100% fill factor).

**Our architecture gives us near 100% fill factor**

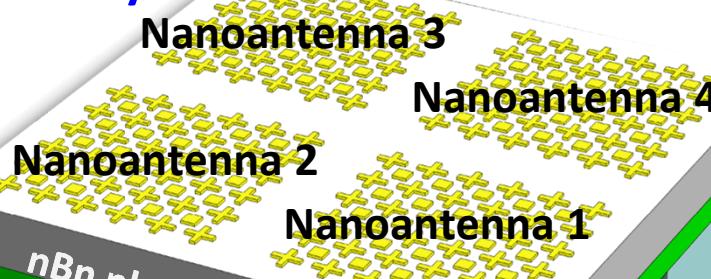
- **Maximizes input signal**
- **Maximizes the resolution**

# Our Current Efforts

## Demonstrate Plasmonic Field Concentration

- Develop methods to accurately tune resonance
- Achieve high responsivity (QE > 70%): a joint modeling and fabrication effort.

2x2 sub-array



<2 $\mu$ m  
thick

## Achieve Dark Current Reduction

- Minimize absorber volume
- Suppress interface parasitics

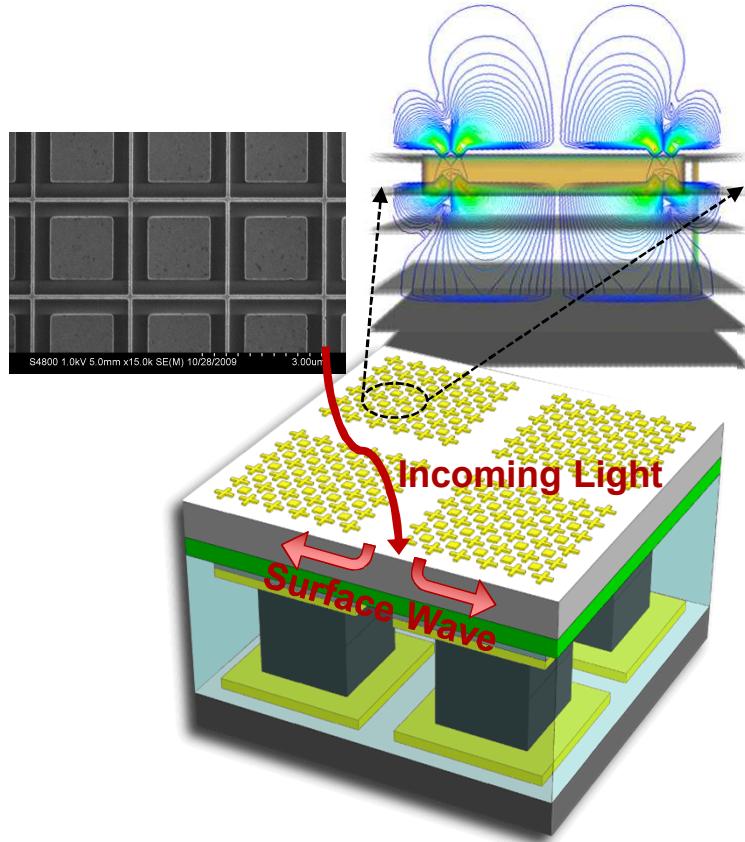
## Develop Integration Methods

- Maintain surface flatness
- Ensure uniform lithography
- Manage material stress

# Demonstrate Plasmonic Field Concentration

# Enabling Technology: Nanoantenna (NA)

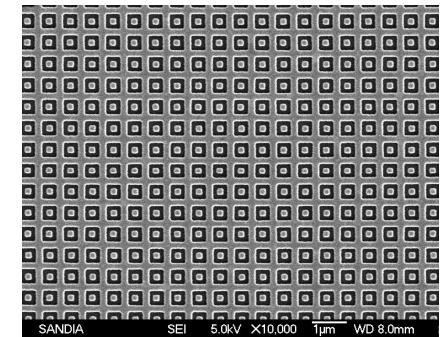
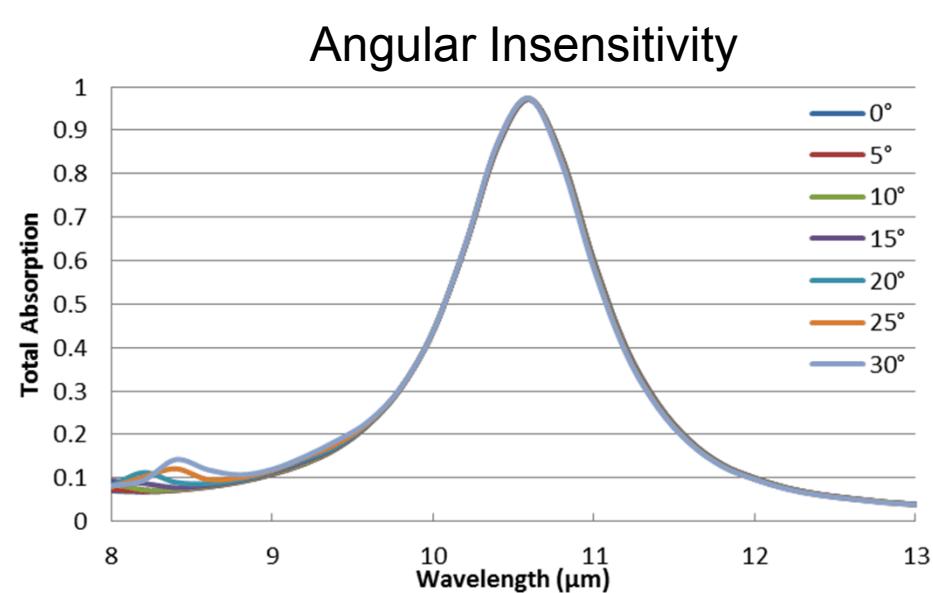
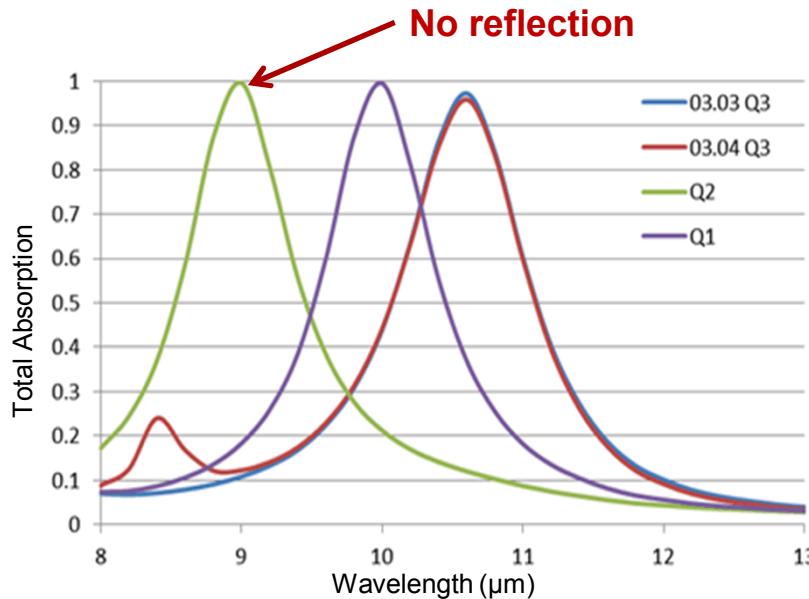
## What is a nanoantenna?



- A subwavelength patterning of metal or high-index dielectric
- The nanoantenna converts incoming radiation to a surface wave with energy confined to a small volume
- The pattern may be changed from pixel-to-pixel allowing adjacent pixels to have different spectral or polarization response
- Built-in A/R “coating”
- Angular insensitivity
- A foundation for tunability

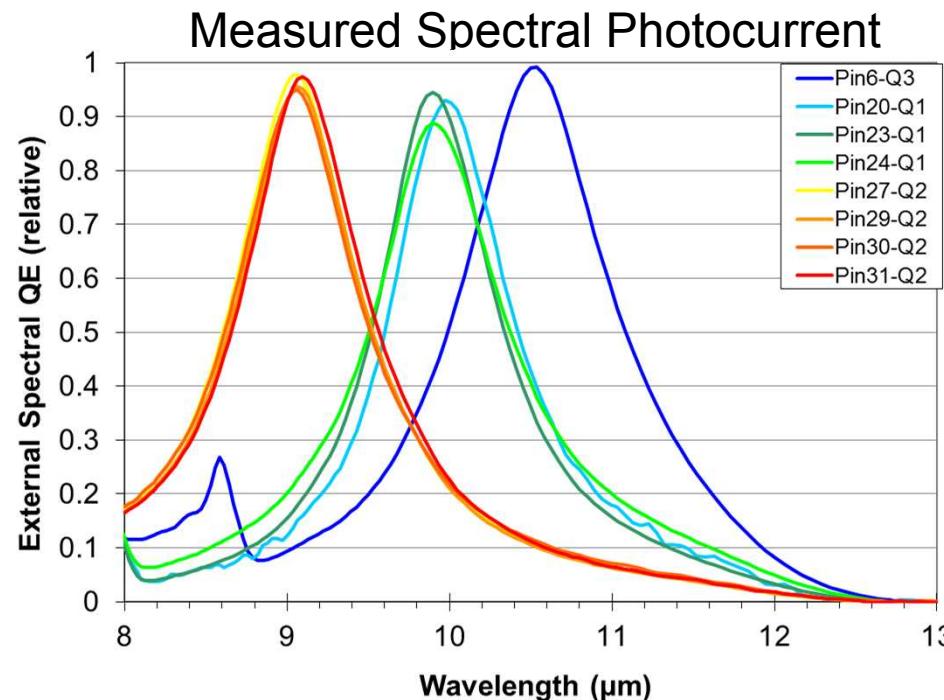
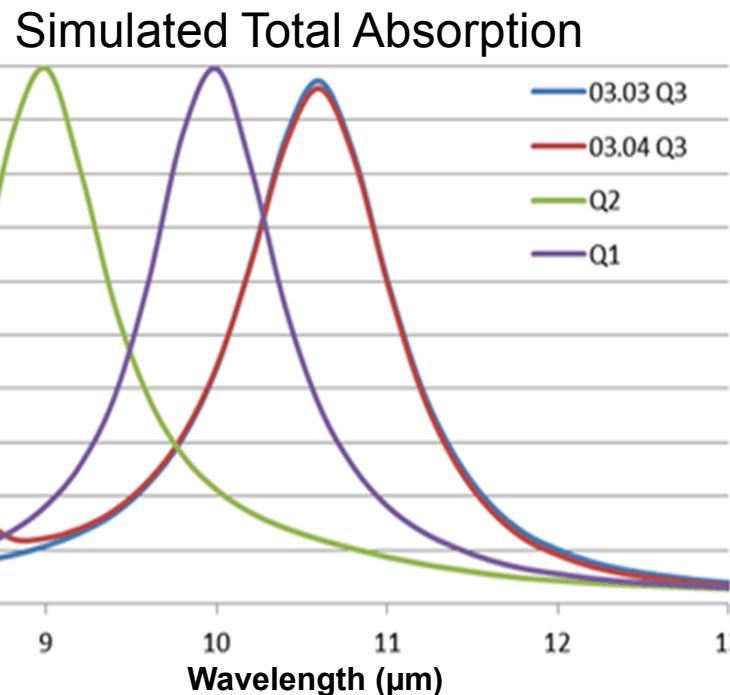
# Nanoantenna Optical Properties

- The nanoantenna couples the incoming light to a surface wave with no reflection at the design wavelength.
  - Achieved with a single patterned metal layer.
  - No AR dielectric stack required
- The AR effect does not change with angle as it would with a dielectric AR coat.
- Polarization independence over angular range of interest.



# Develop Numerical Model for Tuning NA

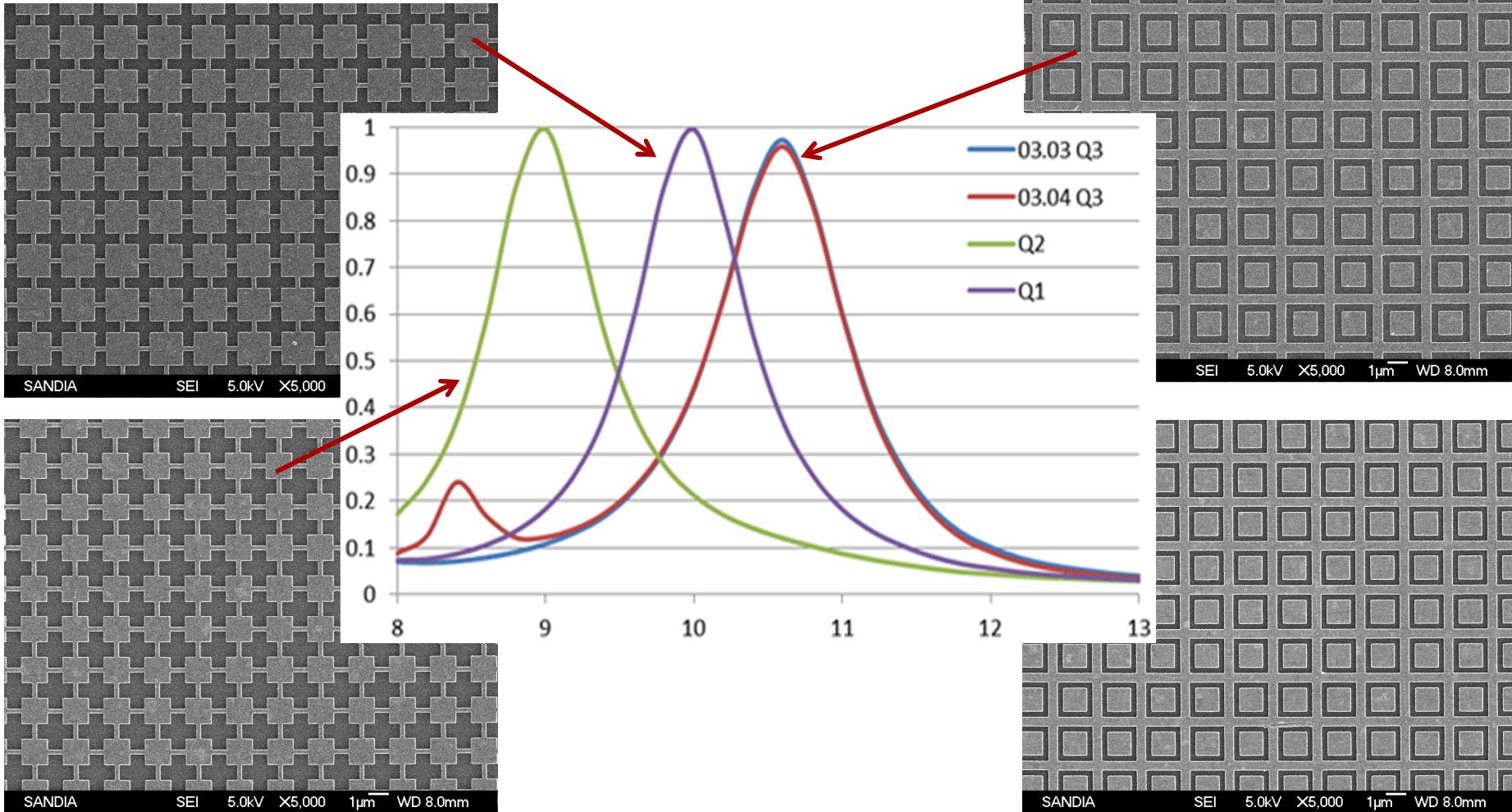
- Early work has confirmed good agreement
- Refine nanoantenna model for QE optimization
- Determine relevant material properties



- Calibrated QE is being measured

# Challenges in the Replication of Design

- Gap feature size difficult to replicate (pitch is accurate)
- Surface flatness difficult to ensure

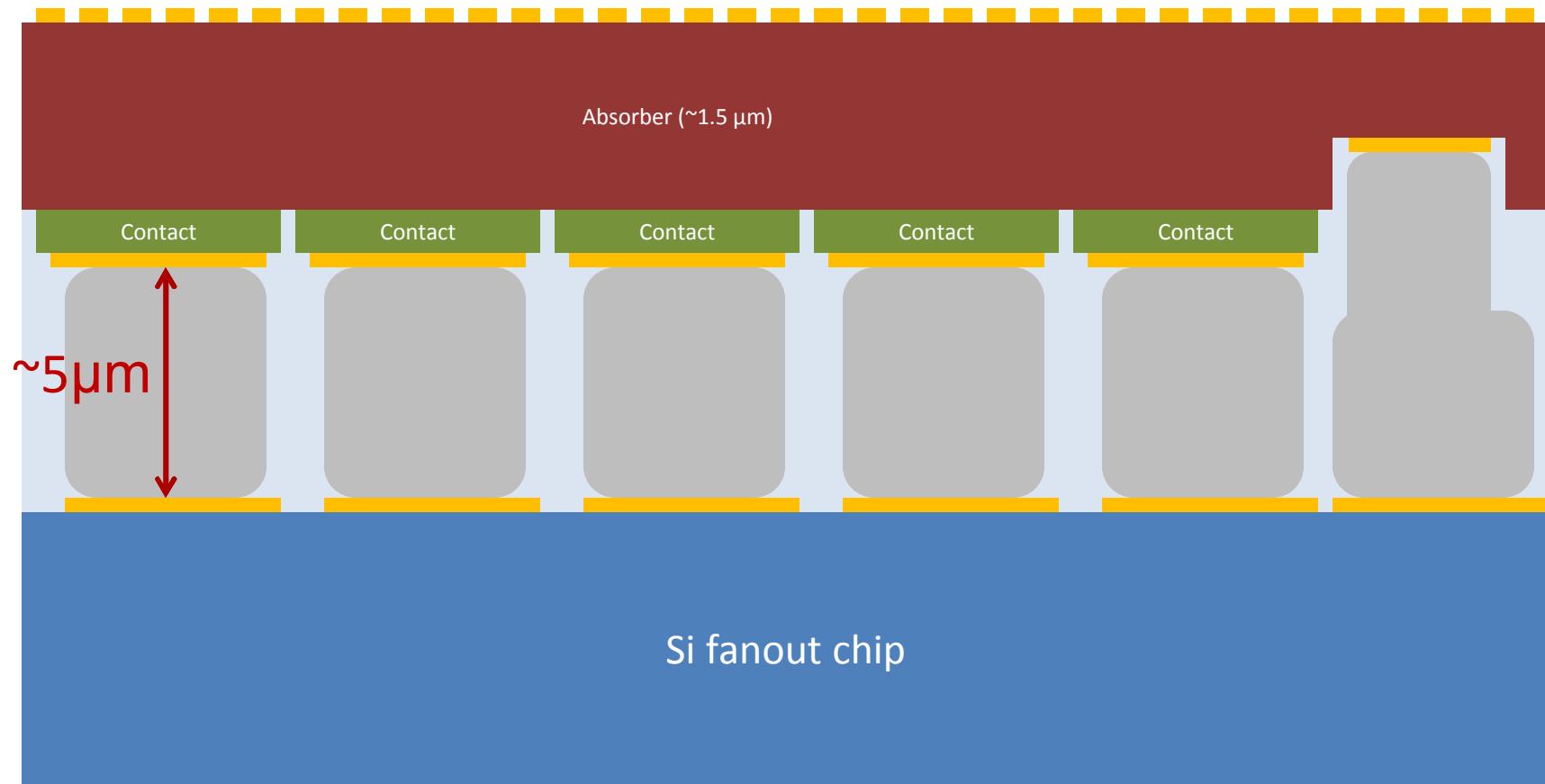


# Challenges in Ensuring Surface Flatness

- Detector epi layers much thinner than indium bumps, epoxy  $\Rightarrow$  small stresses deform the epi

Light  
↓  
↓  
↓

Nanoantenna Pattern

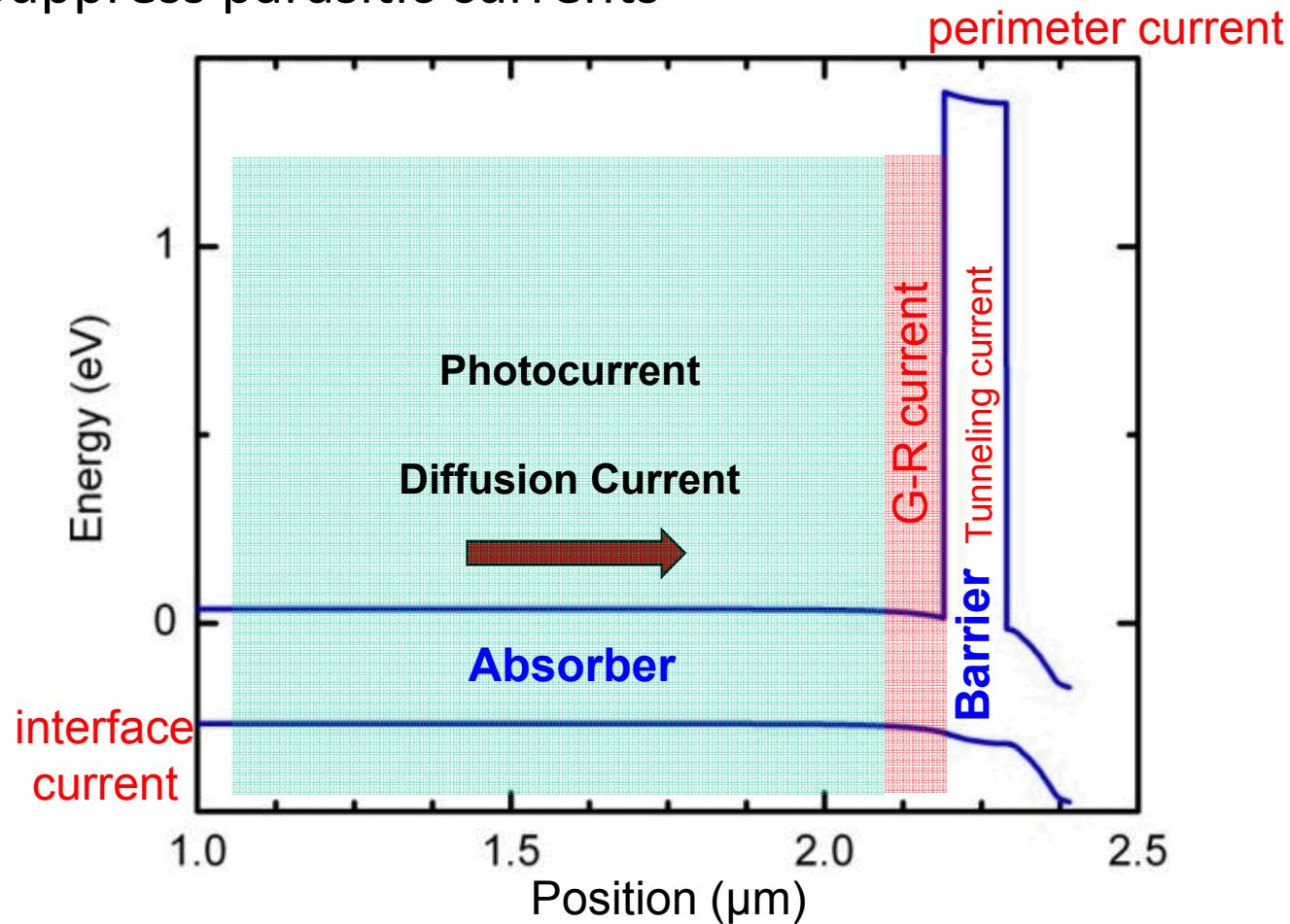


# Achieve Dark Current Reduction

# Achieve Dark Current Reduction

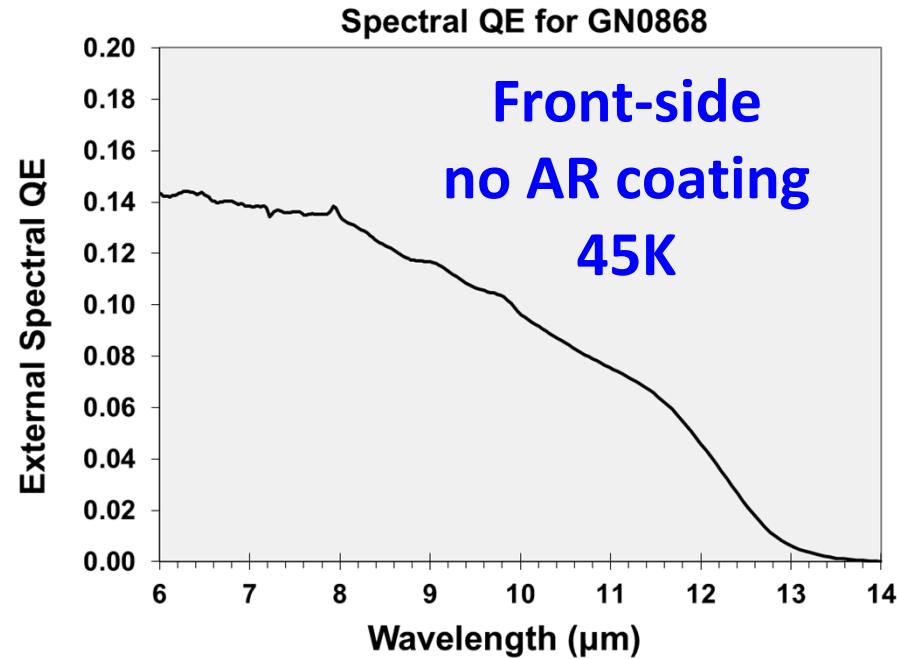
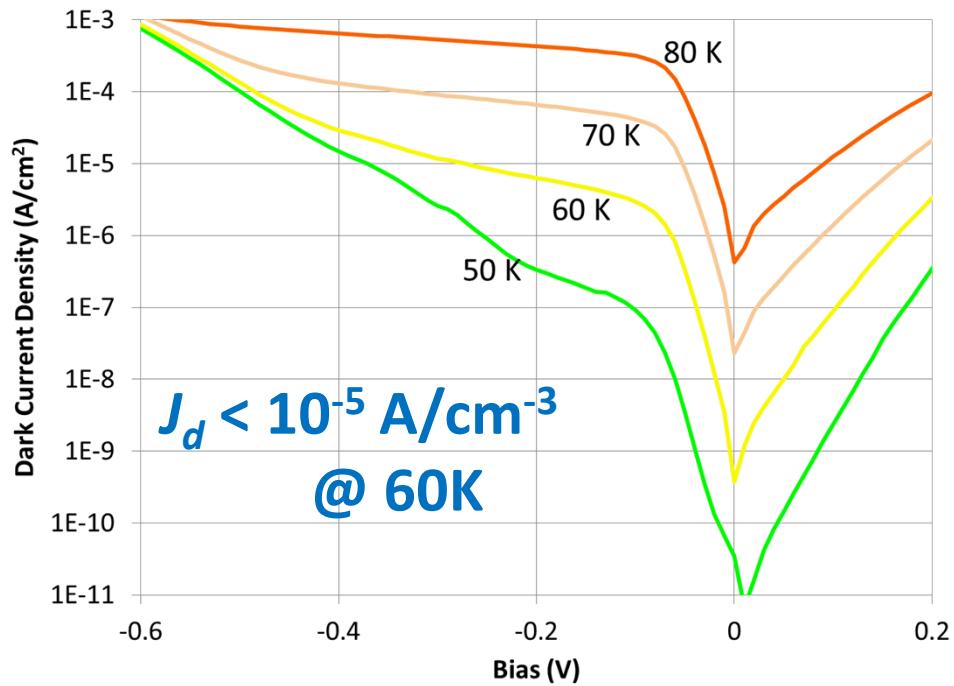
- Based on nBn device architecture
- Minimize absorber volume
- Suppress parasitic currents

$$J_{Diff} = q n_i^2 W_{Abs} / N_D \tau$$



# Limitations of Conventional (V)LWIR nBn

- MWIR nBn FPAs very successful
- $I_{dark}$  & QE approaching HgCdTe
- Compatible w/ tuning methods



- High  $m^*_{hh}$  limits diffusion length
- QE suffers, especially for VLWIR
- Absorber doping exacerbates the problem
- Very difficult problem to solve

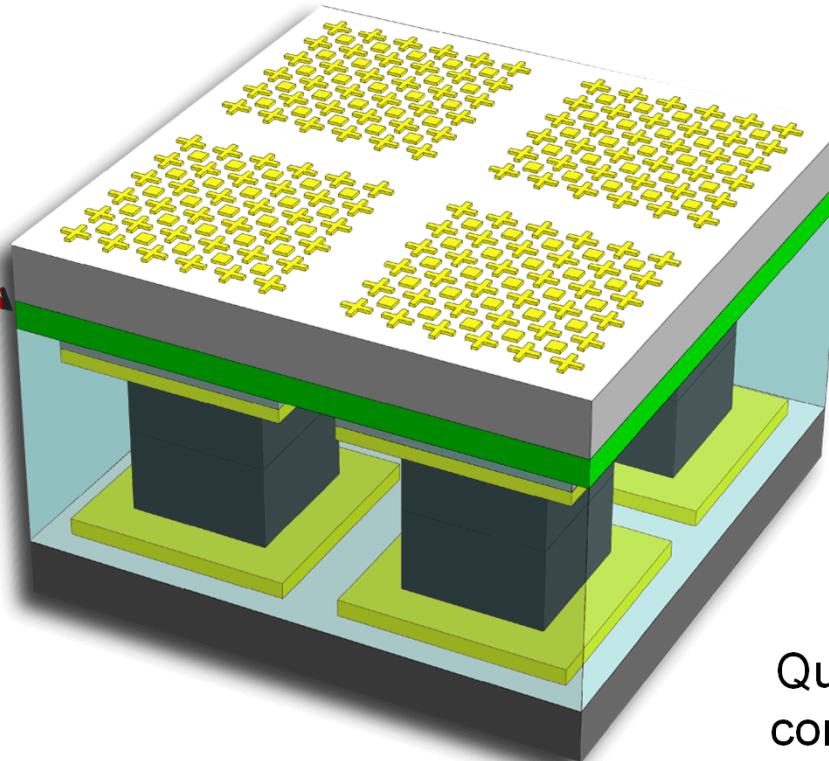
# Features of NA-nBn FPA

Built-in “AR coating”      Angular insensitivity

Control perimeter  
current by leaving  
Barrier intact

Thin absorber  
ensures high MTF  
(low crosstalk)

Field concentration  
ensures high QE

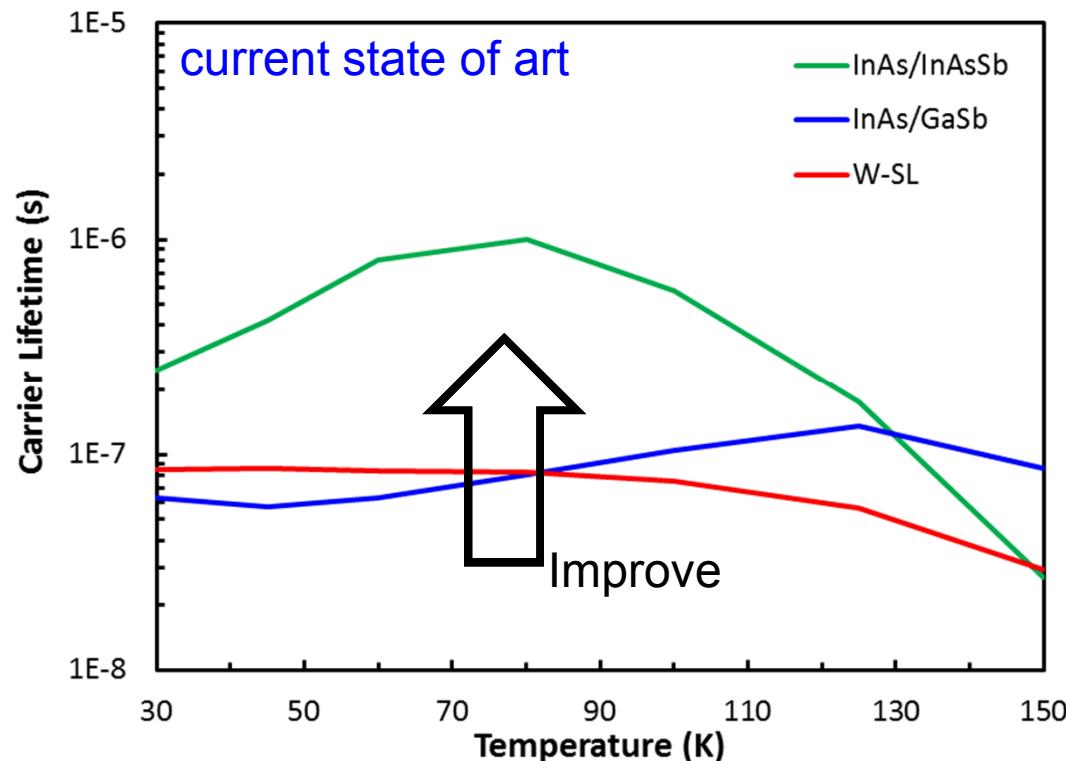


Quantum Efficiency:  
competition between  
metal and semiconductor  
absorption  $\Rightarrow$   
Absorbers with stronger  
absorption desired

# Absorber Material Choices

- W-SL: high absorption strength, low mobility
- InAs/InAsSb: longest lifetime, low mobility
- InAs/GaSb: somewhere in between

$$J_{Diff} = q n_i^2 W_{Abs} / N_D \tau$$

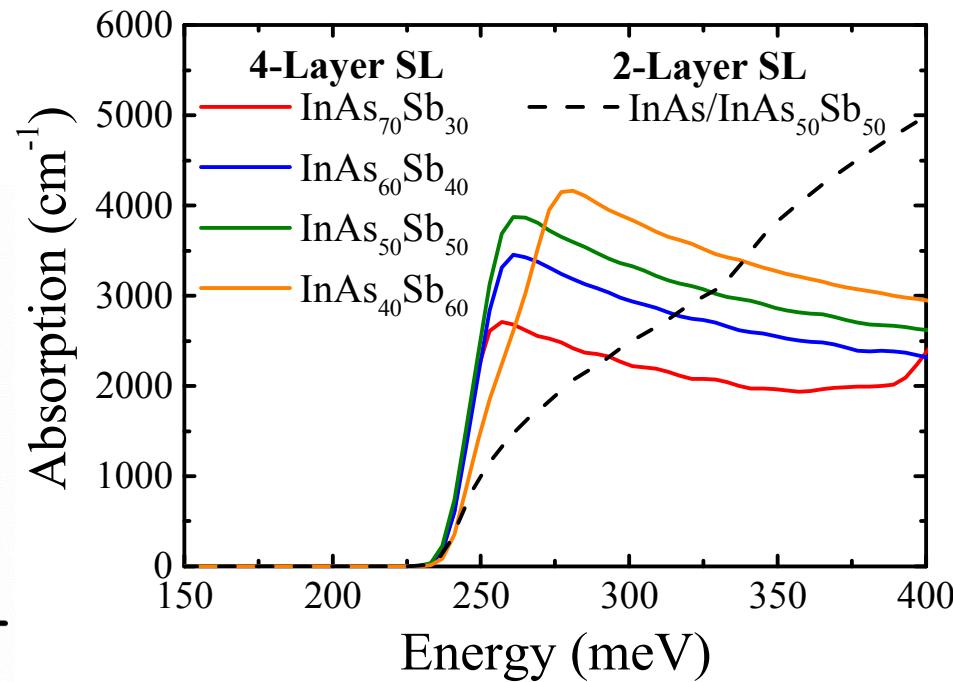
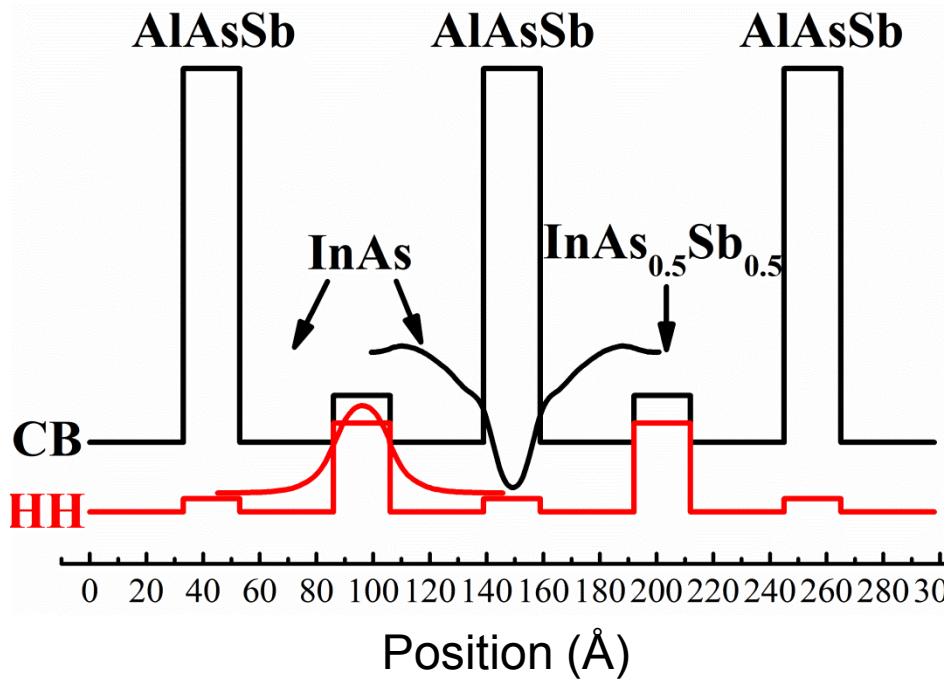


- Down-select in 12 months

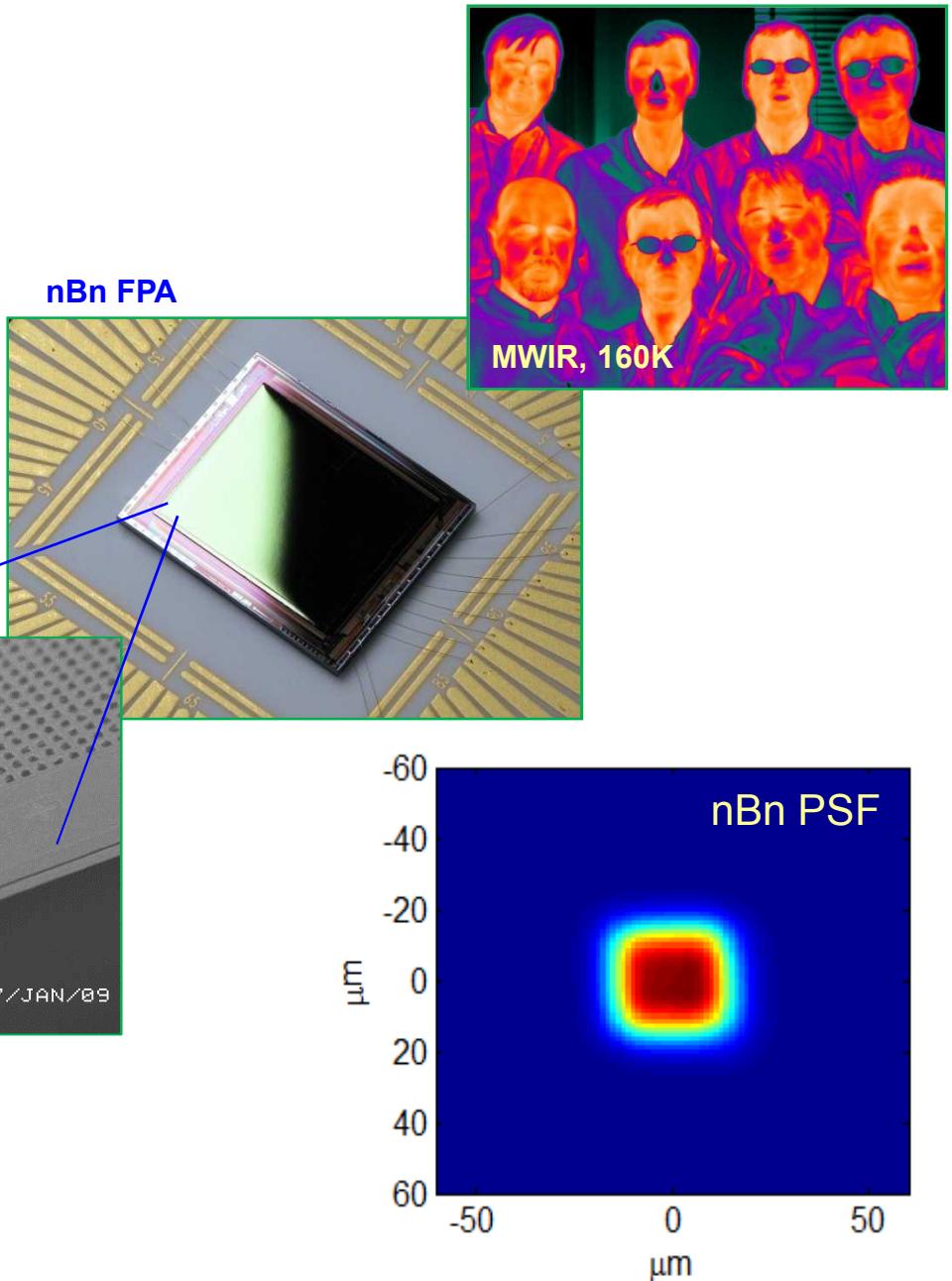
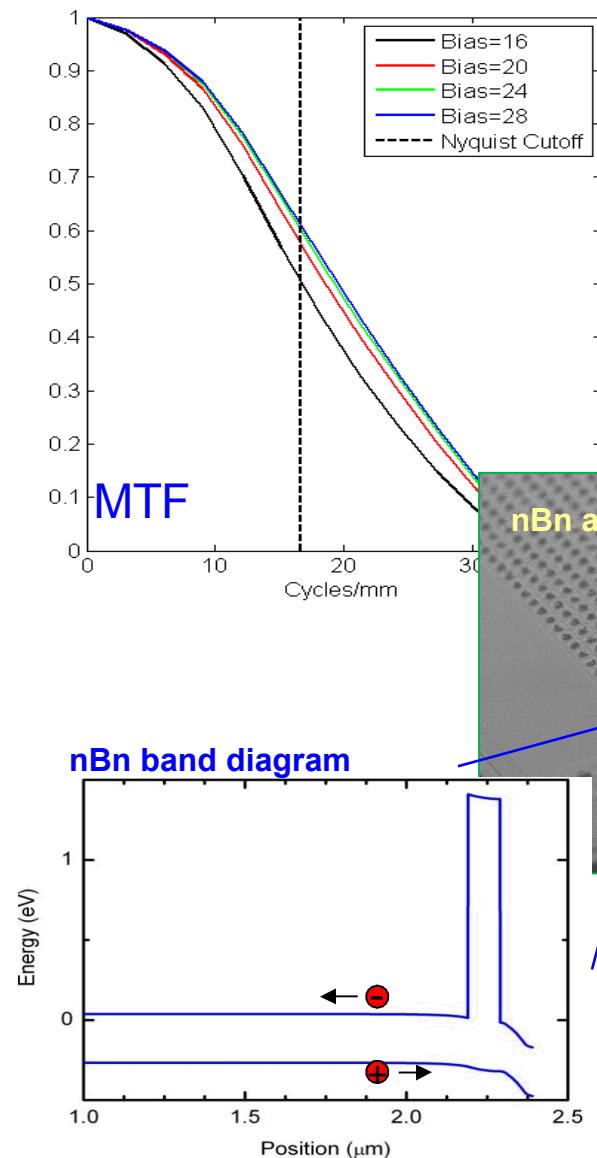
# W-SL Properties

- AlAsSb bisects electron wavefunction
- Higher e-h overlap than InAs/InAsSb SL
- Induces “resonant” absorption
- High hole effective mass

Modified from NRL design

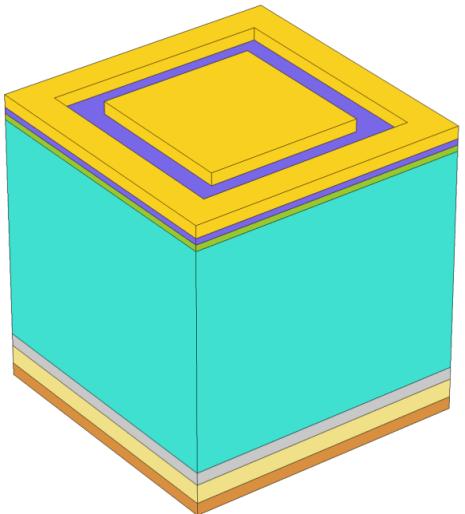


# Sandia nBn R&D

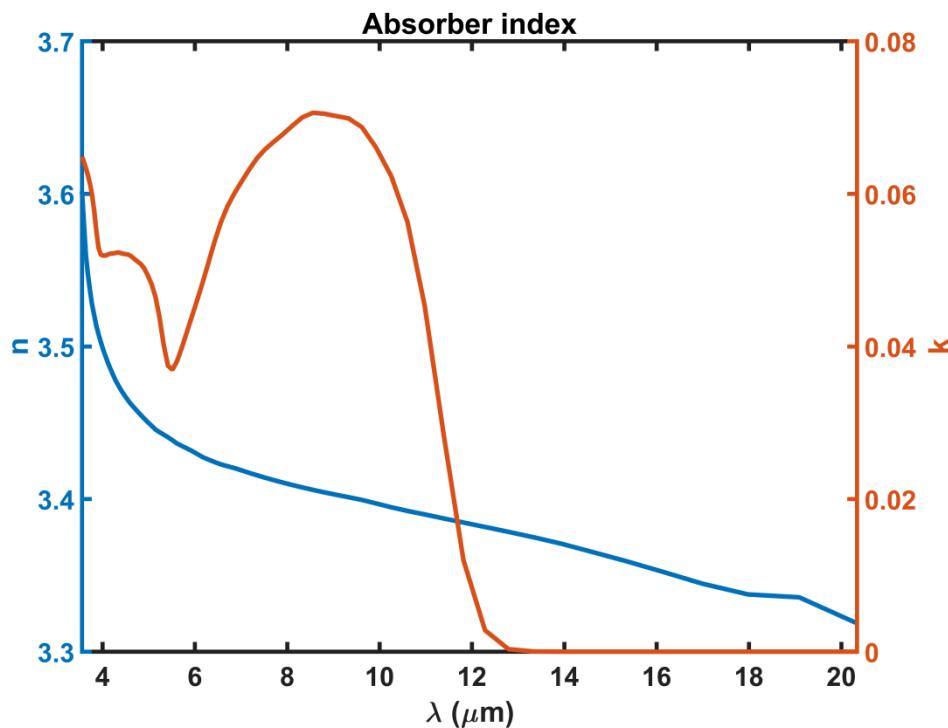


# Electromagnetic and Electrostatic Modeling

# Comsol Device Modeling

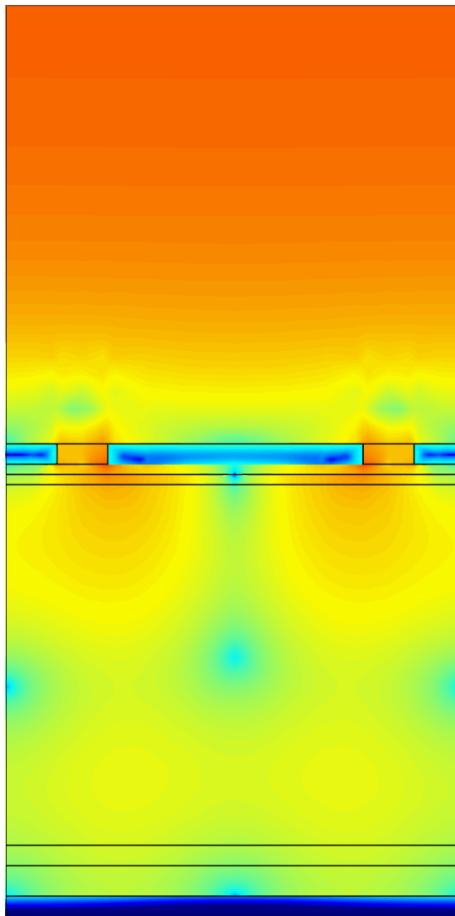


- Gold
- GaSb
- AlAsSb
- Absorber
- AlGaAsSb
- InAsSb
- AlCu

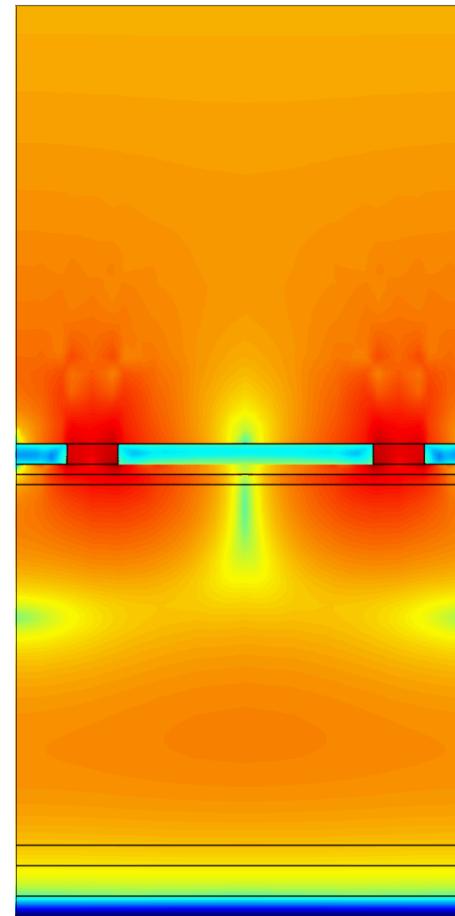


# Electric field distribution

8  $\mu\text{m}$



10.75  $\mu\text{m}$



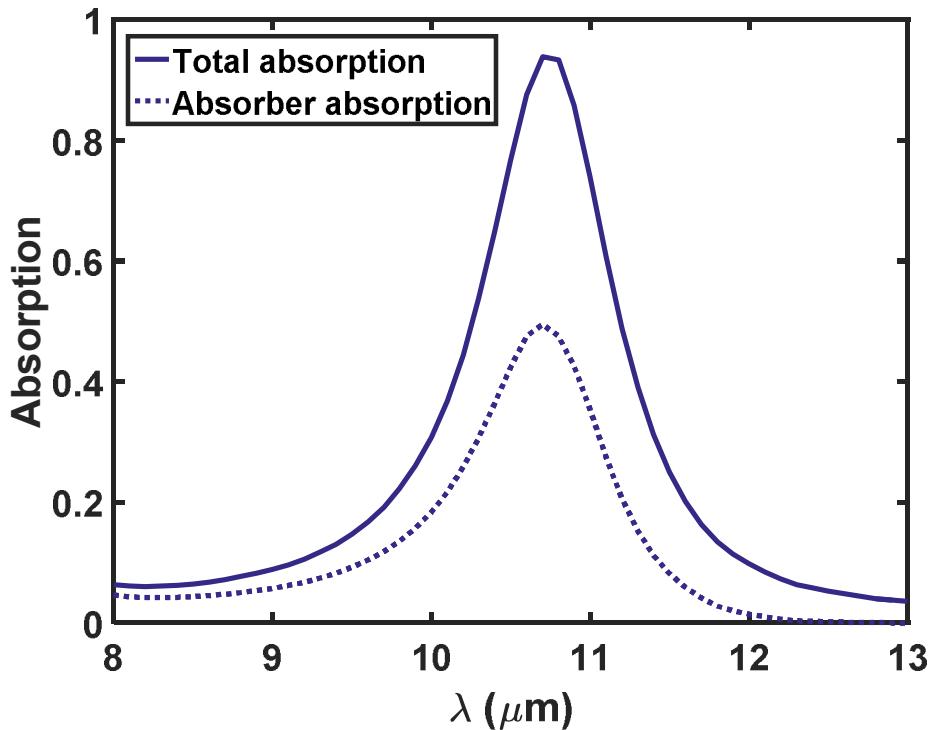
$\text{Log}(|E|)$

8.5



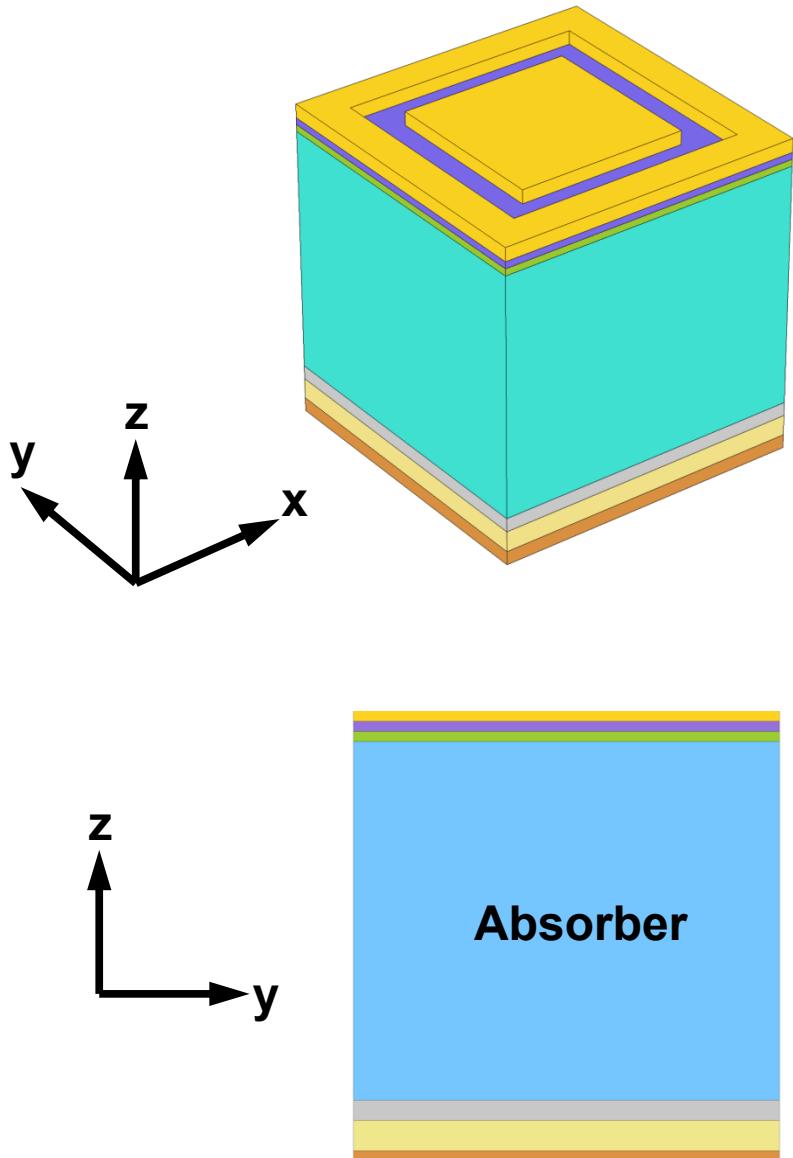
3.5

# Absorption Location

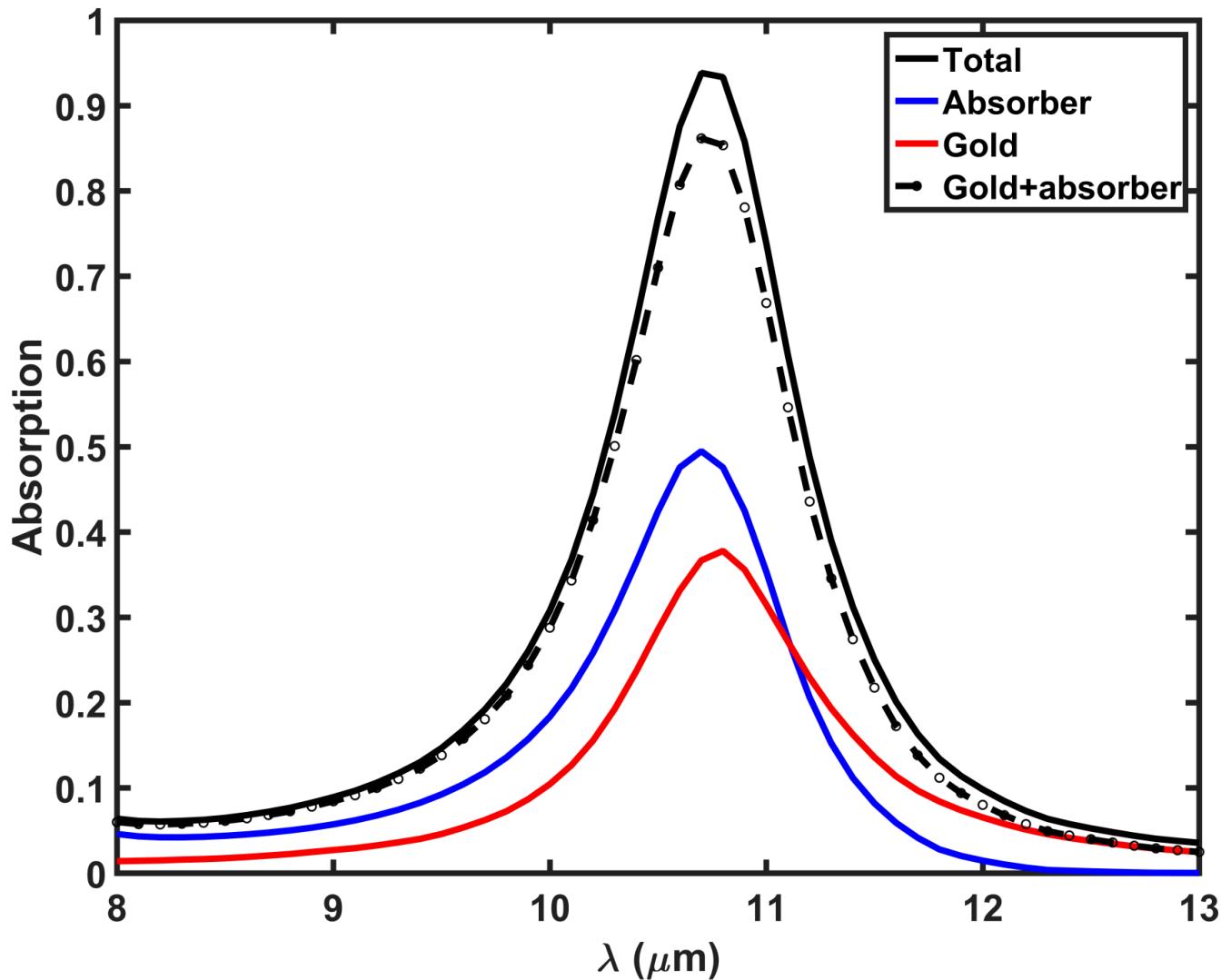


Flux through top and bottom surface:

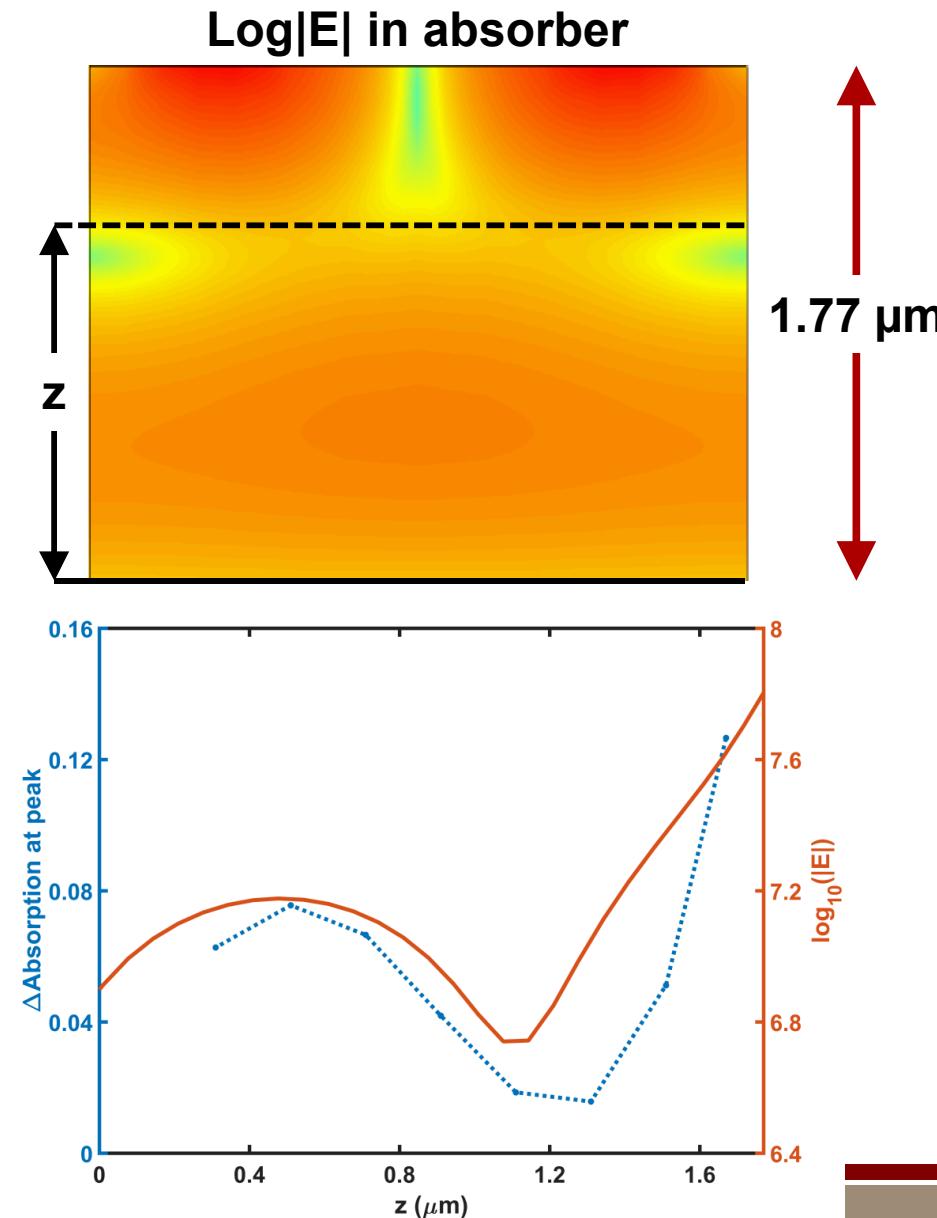
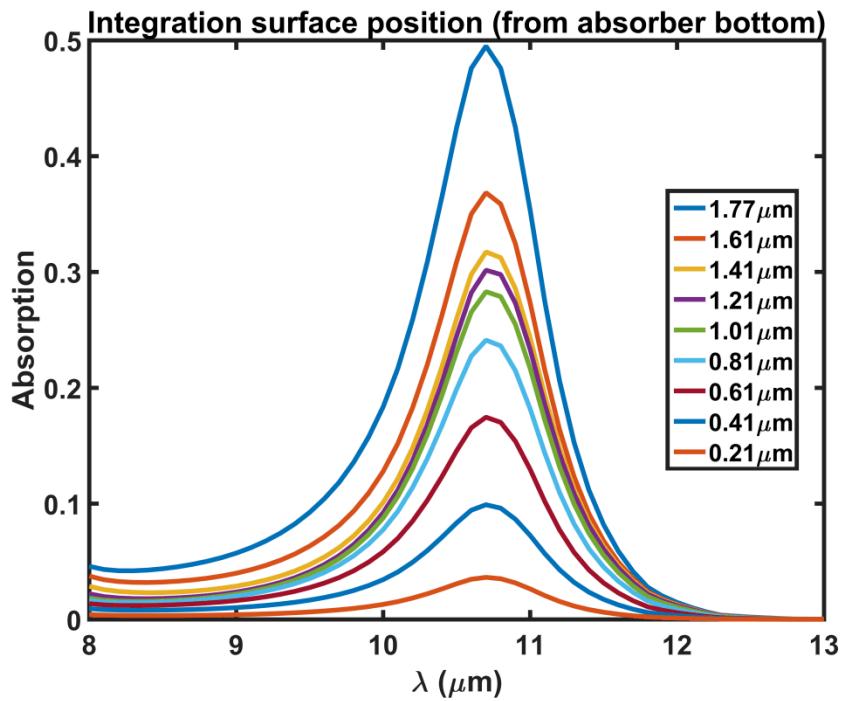
$$A_{\text{abs}} = \int_{\text{top}} S_z dx dy - \int_{\text{bot}} S_z dx dy$$



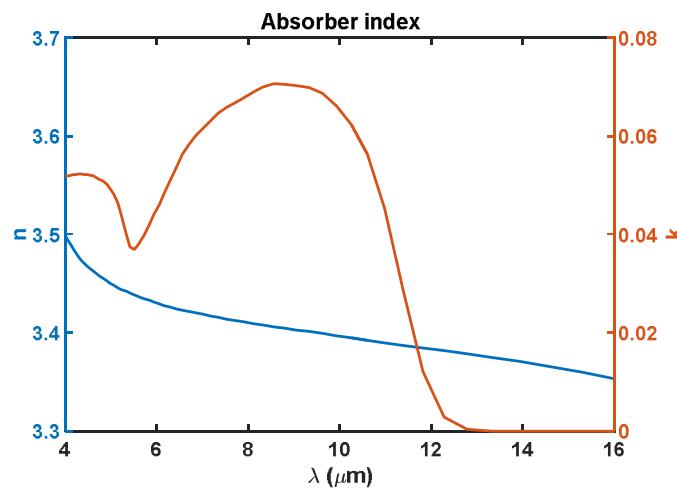
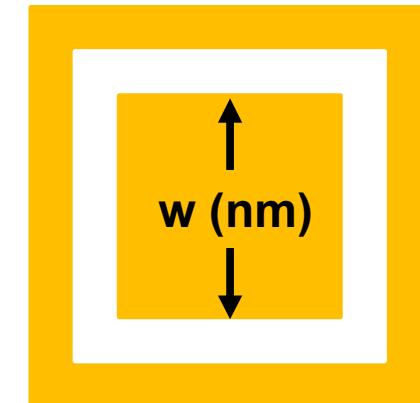
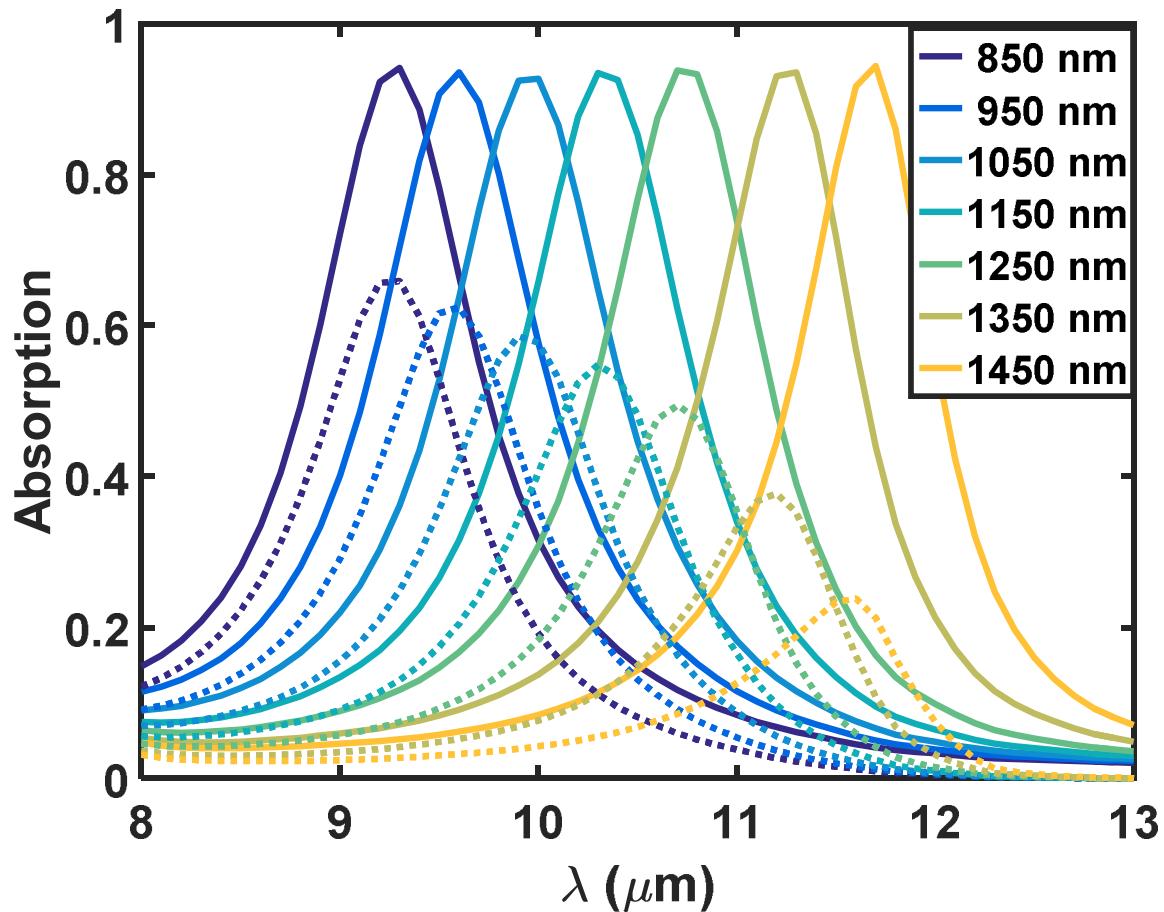
# Absorption Location



# Absorption Location



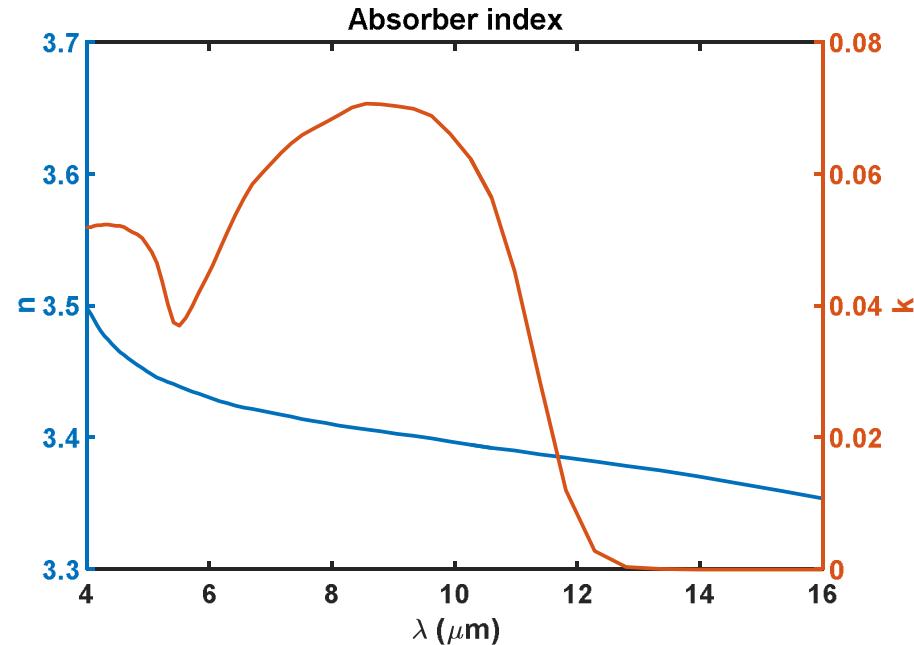
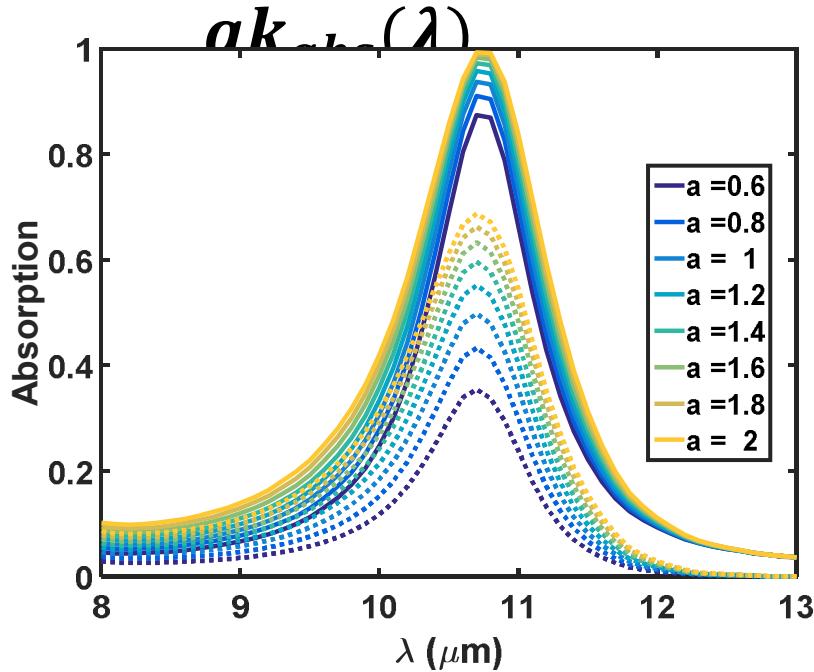
# Shifting absorption resonance



**Modifying  $w$  allows for shifting of the resonance of the nanoantenna array**

# Optimizing absorber index

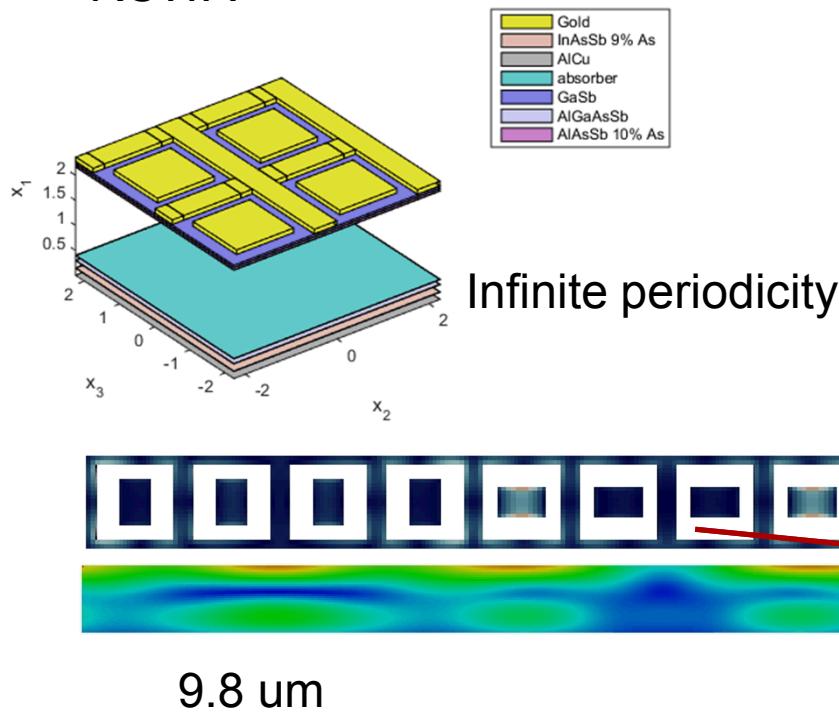
Scaling the absorber index:  $k_{\text{abs}} =$



Higher absorber  $k$  yields greater “useful” absorption

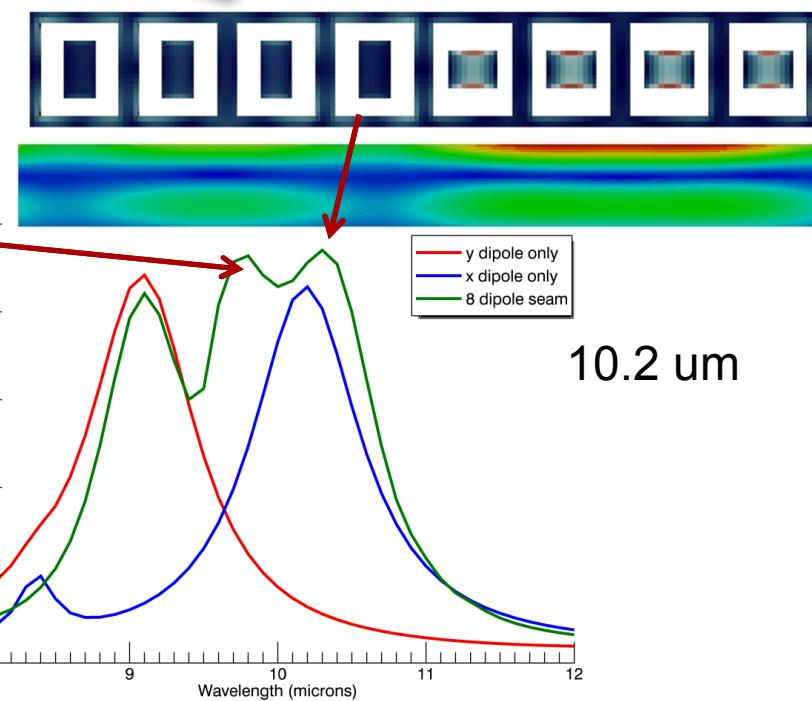
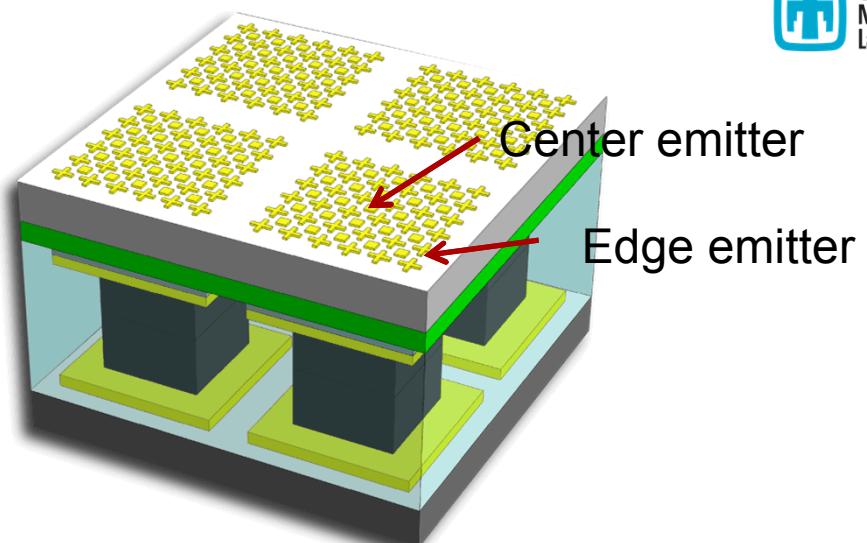
# Finite Pixels

RCWA



Dipole Seams: effect of non-periodicity  
on absorption.

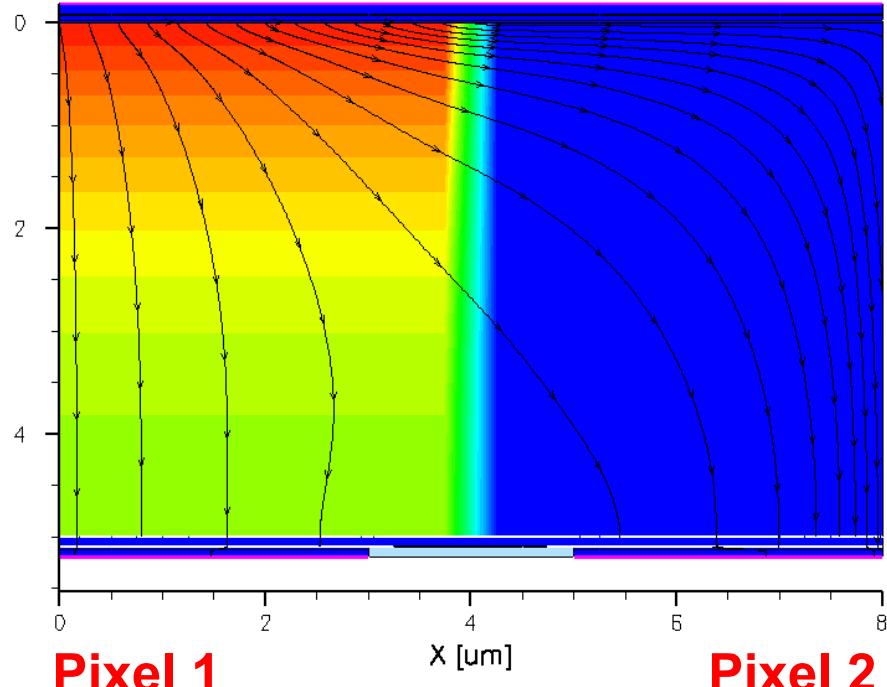
Center to edge differences can lead to  
cross-talk



# 2-D Numerical Device Simulation Capability

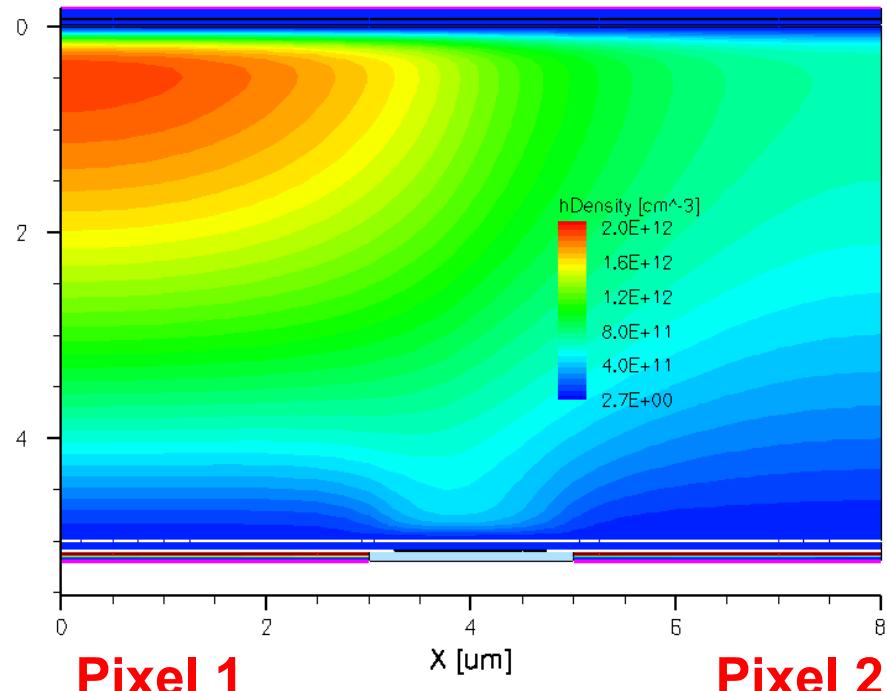
Current Paths

Illumination



Hole Density Contour

Illumination



Useful for analyzing 2-D effects: crosstalk,  
optical concentrator.

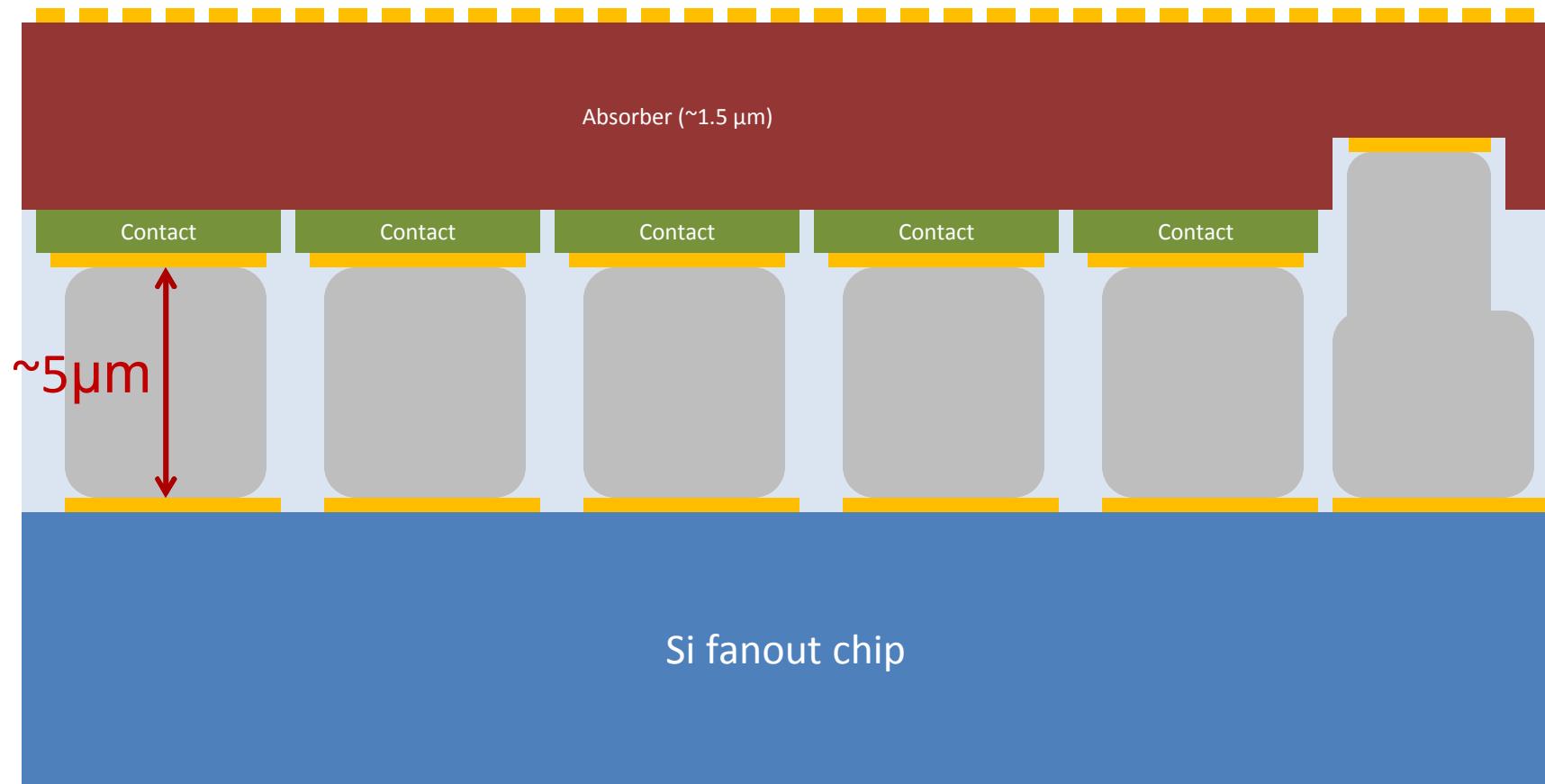
# Develop Integration Methods

# Challenges in Ensuring Surface Flatness

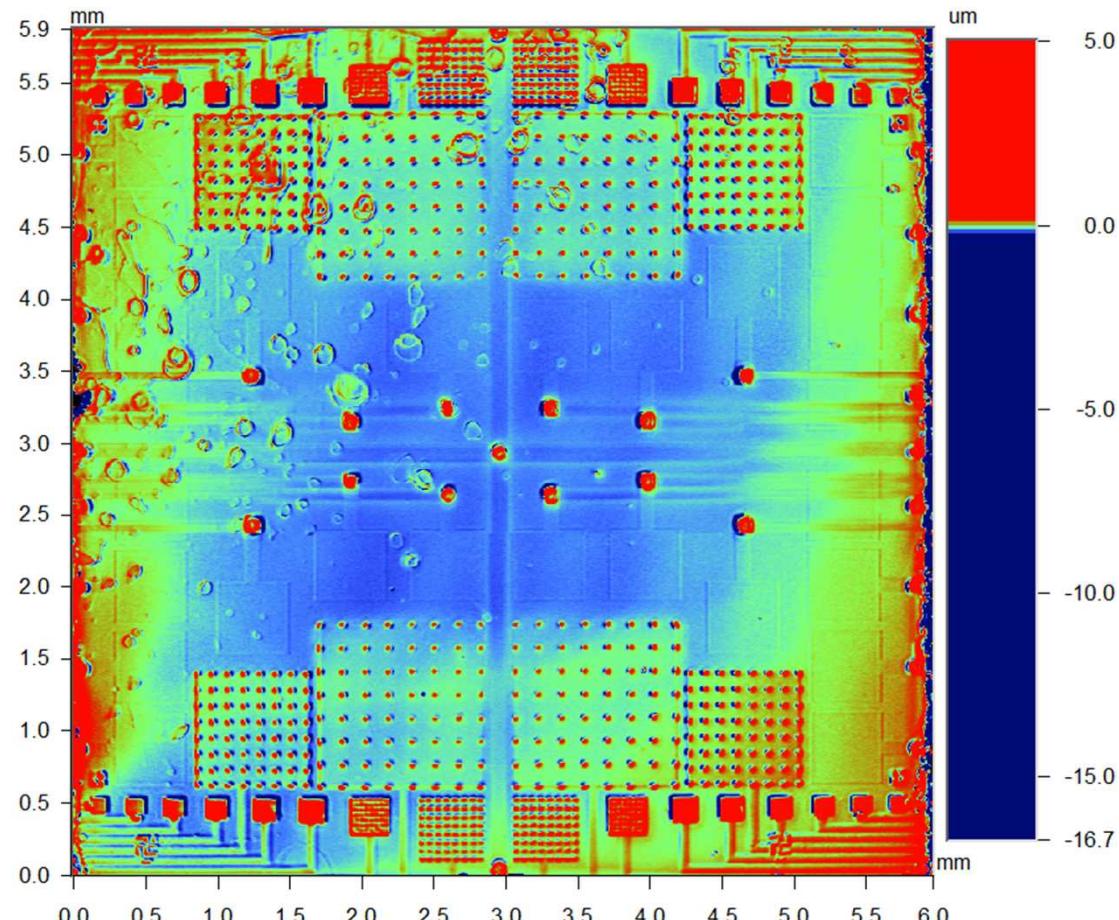
- Detector epi layers much thinner than indium bumps, epoxy  $\Rightarrow$  small stresses deform the epi

Light  
↓  
↓  
↓

Nanoantenna Pattern



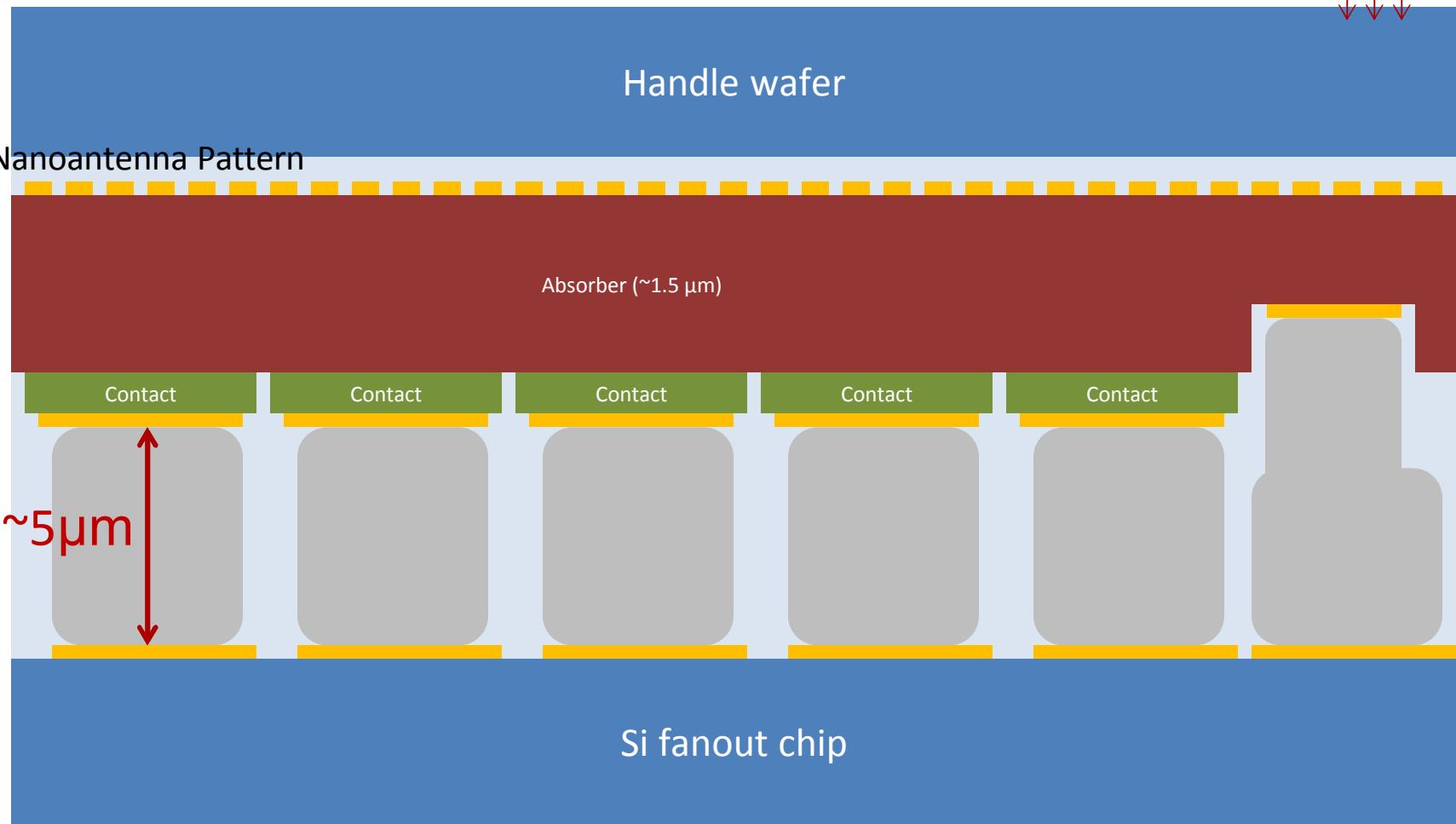
# Surface Flatness Issues



- Large topography issues with isolated bumps
  - This creates issues with writing the nanoantennas
  - May hinder detector performance due to material stresses
- Dense arrays show reduced topography
  - Similar to an array for mating to a ROIC

# Alternate Integration Method

- Transferring detector materials to a carrier should help maintain surface planarity



# Summary

- Overall Goal: Demonstrate significantly better performance (dark current, responsivity, MTF) over conventional IR FPAs
- Goal: Characterize sources and mechanisms of dark current in thin absorbers
- Modeling optical fields and carriers
- Formulated approach, Assembled technology components
- Demonstrated ability to tune nanoantenna to LWIR
- Demonstrated progress toward suppressing parasitic  $I_{dark}$
- Identified areas of greatest technical challenge: integration